



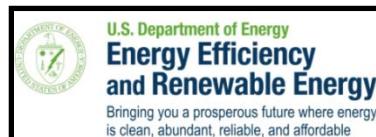
Beyond A/B/A/B... Unorthodox Pulse Sequences in Atomic Layer Deposition

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Energy Systems Division

Argonne National Laboratory

Argonne, IL, USA



2012 NNIN ALD Symposium
Cambridge, MA, November 30, 2012



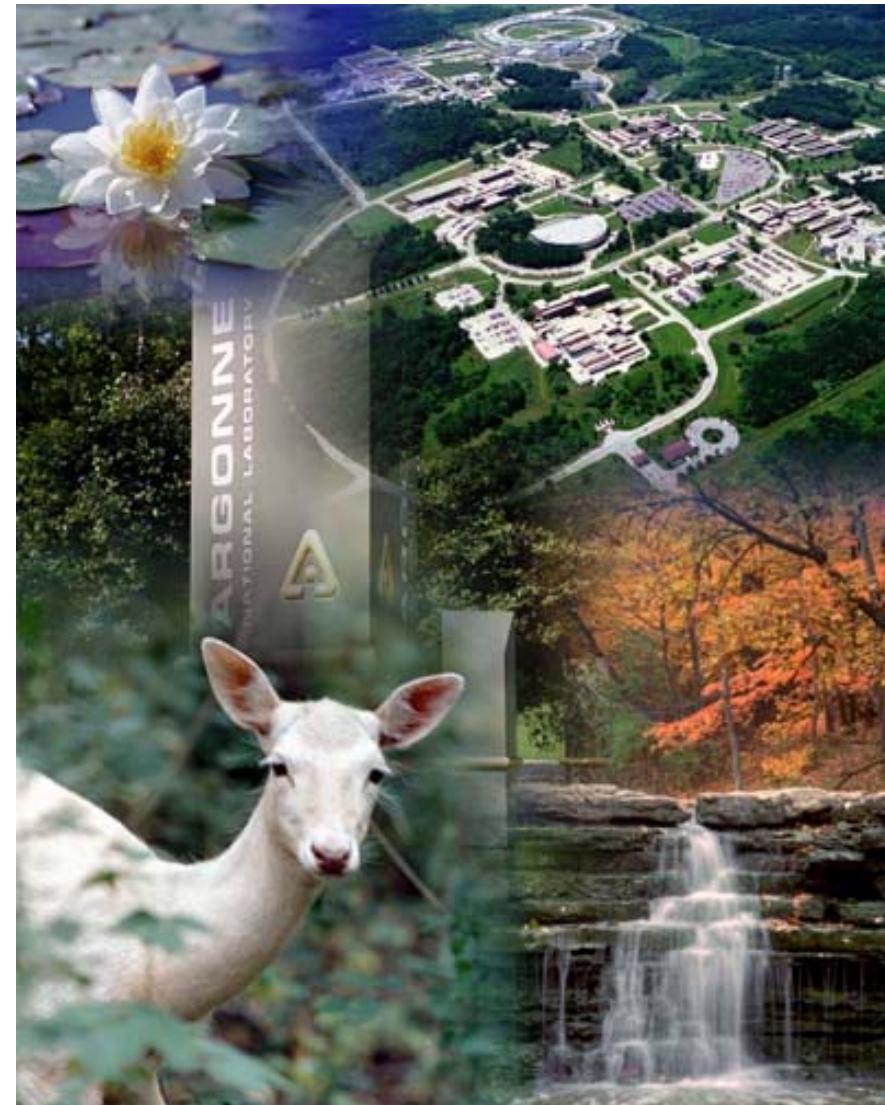
Outline

- Introduction
 - Argonne National Laboratory
 - Traditional ALD, A/B/A/B...
- Beyond A/B/A/B...
 - Stripe Coating
 - Surface Poisoning
 - Precursor Synergy
 - Nanobowls
- Conclusions



Argonne National Laboratory

- Founded in 1943, designated a national laboratory in 1946
- Managed by The University of Chicago for the U.S. Department of Energy
 - More than 2,800 employees and 5,000+ facility users
 - 1,500-acre, wooded site in DuPage County, Illinois
 - 25 miles southwest of Chicago, Illinois



Argonne User Facilities



■ Leadership Computing Facility “Blue Gene”



■ Advanced Photon Source



■ Center for Nanoscale Materials



■ Argonne Tandem-Linac Accelerator Facility

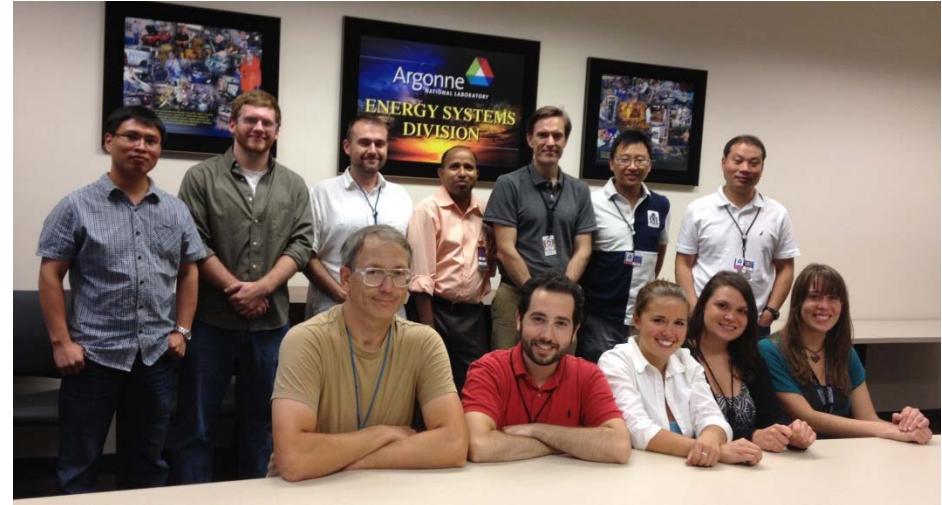


■ Electron Microscopy Center

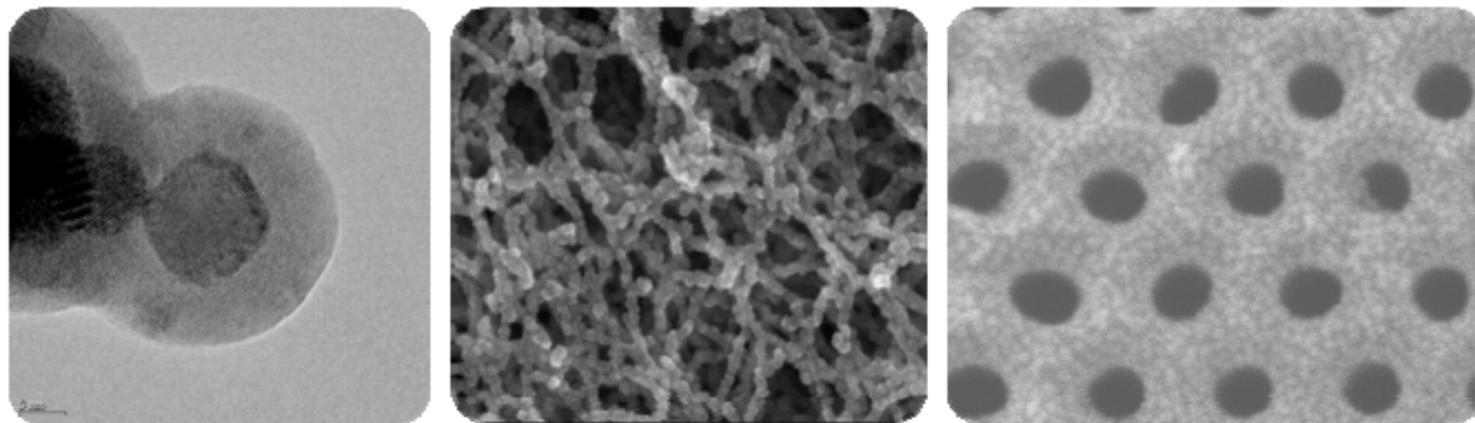


Argonne Atomic Layer Deposition Group

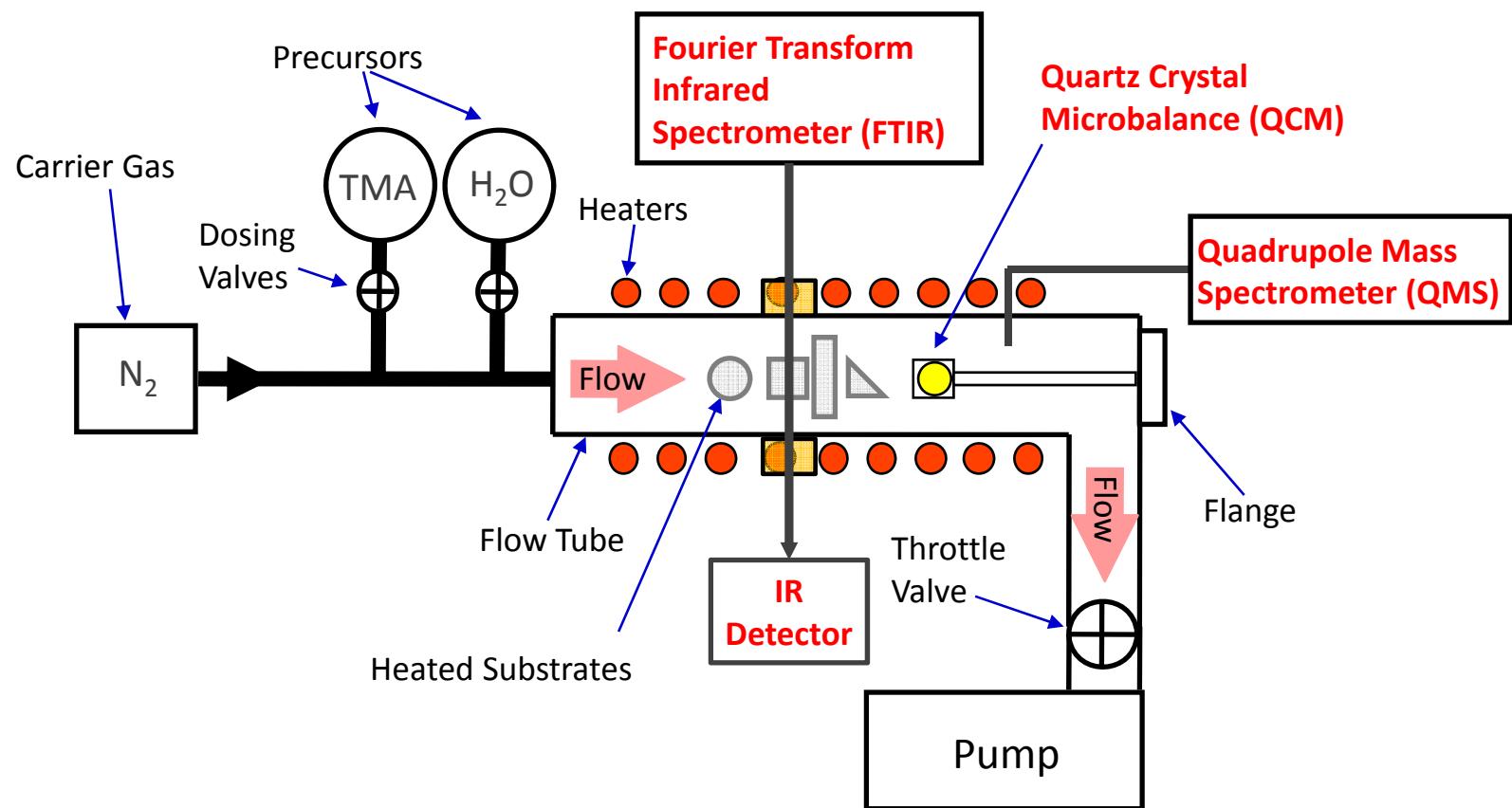
- Develop ALD technology
- Apply ALD to emerging applications:
 - Solar Cells
 - Large Area Photodetectors
 - Lithium Batteries
 - Catalysis



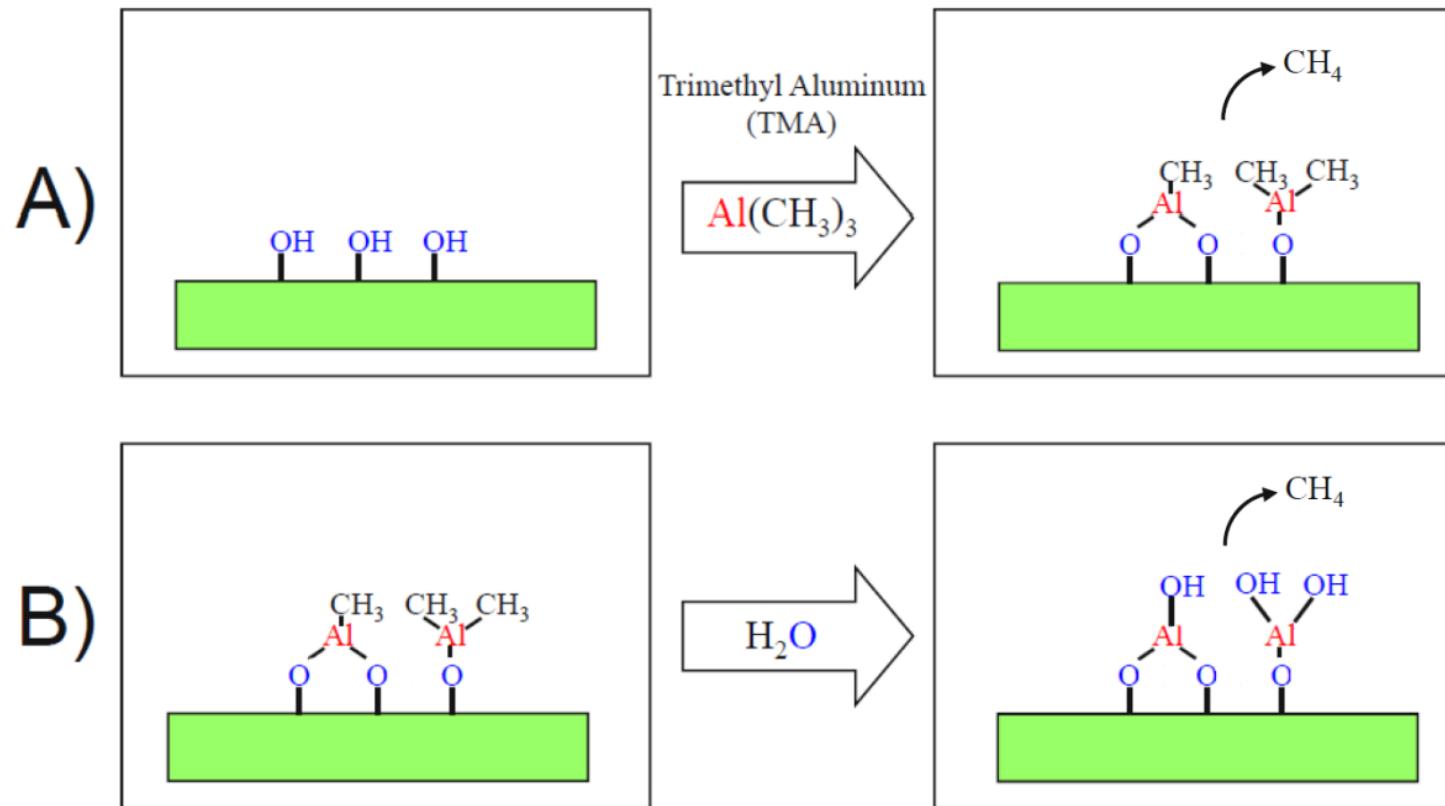
Precise coatings on porous templates:



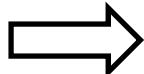
Components of Argonne ALD Systems



Traditional ALD, A/B/A/B...



Self-limiting
A/B/A/B...
surface
chemistry



- thickness control
- composition control
- uniformity
- conformality
- pinhole-free
- low-temperature
- high purity



Many Examples of A/B/A/B...

Puurunen, J. Appl. Phys. **87**, 121301 (2006)

TABLE III. Overview of ALD processes based on two reactants (Source: ISI Web of Science, status in February 2005). Description of the ligands in Fig. 4.

Z	Material	Reactant A ^a	Reactant B	Refs.
5 Boron				
	B ₂ O ₃	BBr ₃	H ₂ O	85
	BN	BCl ₃	NH ₃	158
		BBr ₃	NH ₃	159
	B _x P _y O _z	B(OMe) ₃	POCl ₃	88 and 89



(8 pages!)

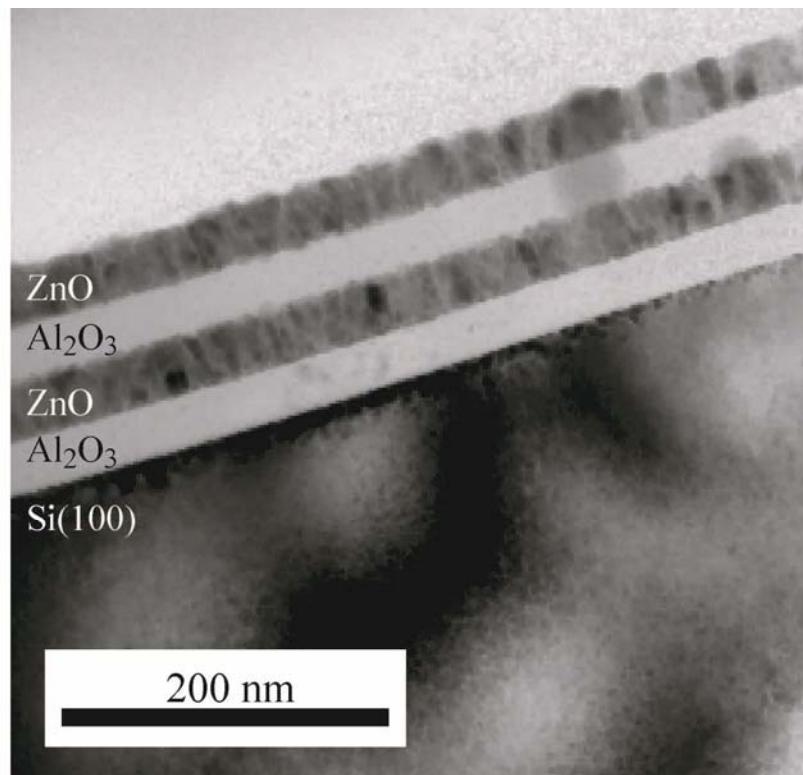
PbS	PbBr ₂ PbI ₂ Pb(OAc) ₂ Pb(O'Bu) ₂ Pb ₄ O(O'Bu) ₆ Pb(thd) ₂ Pb(dedtc) ₂	H ₂ S H ₂ S H ₂ S H ₂ S H ₂ S H ₂ S H ₂ S	1083 1083 1083 1084 1084 1083 and 1084 1083 and 1084
83 Bismuth	BiO _x	Bi[N(SiMe ₃) ₂] ₃	H ₂ O



Beyond A/B/A/B... - Blended Materials

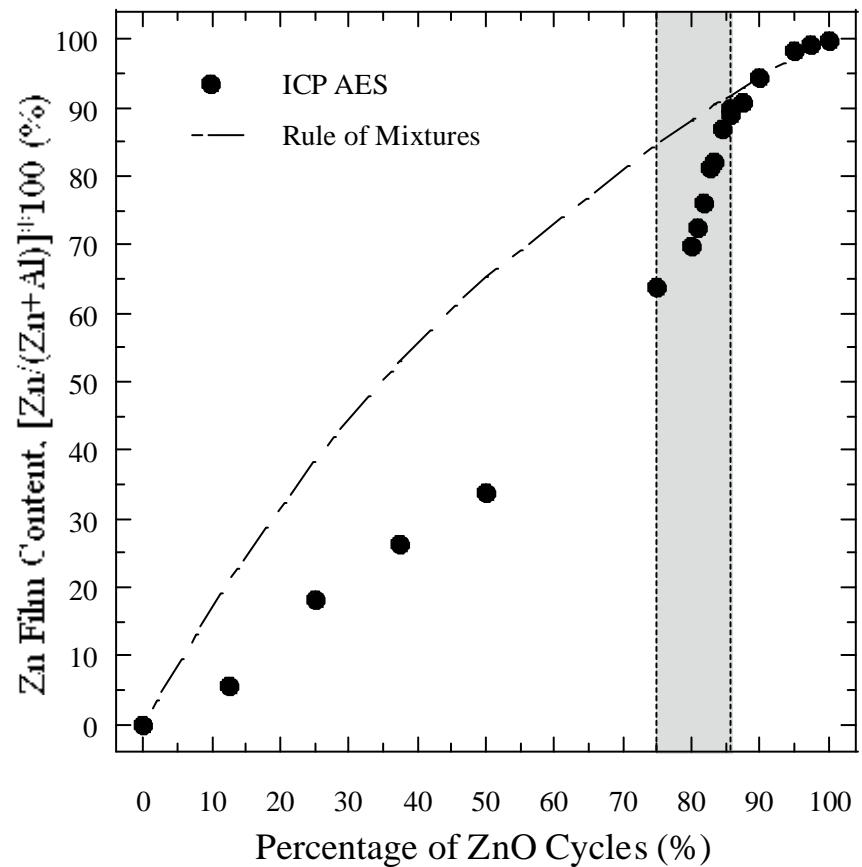
- $\text{TMA} + \text{H}_2\text{O} \rightarrow \text{Al}_2\text{O}_3$
- $\text{DEZ} + \text{H}_2\text{O} \rightarrow \text{ZnO}$

Laminates



Elam, Thin Solid Films **414**, 43, (2002).

Alloys



Elam, Chem. Mater. **15**, 1020, (2003).



Beyond A/B/A/B... - New Processes

Electrochemical and Solid-State Letters, **9** (7) F64-F68 (2006)
1099-0062/2006/9(7)/F64/5/\$20.00 © The Electrochemical Society

Effect of Surface Reactive Site Density and Reactivity on the Growth of Atomic Layer Deposited WN_xC_y Films

A. Martin Hoyas,^{a,b,z} C. M. Whelan,^{a,*} J. Schuhmacher,^a J. P. Celis,^c and
K. Maex^{a,b}

^aIMEC, BE-3001 Leuven, Belgium

^bDepartment of Electrical Engineering, Katholieke Universiteit Leuven , BE-3001 Leuven, Belgium

^cDepartment of Metallurgy and Materials Engineering, Katholieke Universiteit Leuven, BE-3001 Leuven,
Belgium

- A/B/C...
- $\text{B}(\text{C}_2\text{H}_5)_3/\text{WF}_6/\text{NH}_3 \rightarrow \text{WN}_x\text{C}_y$



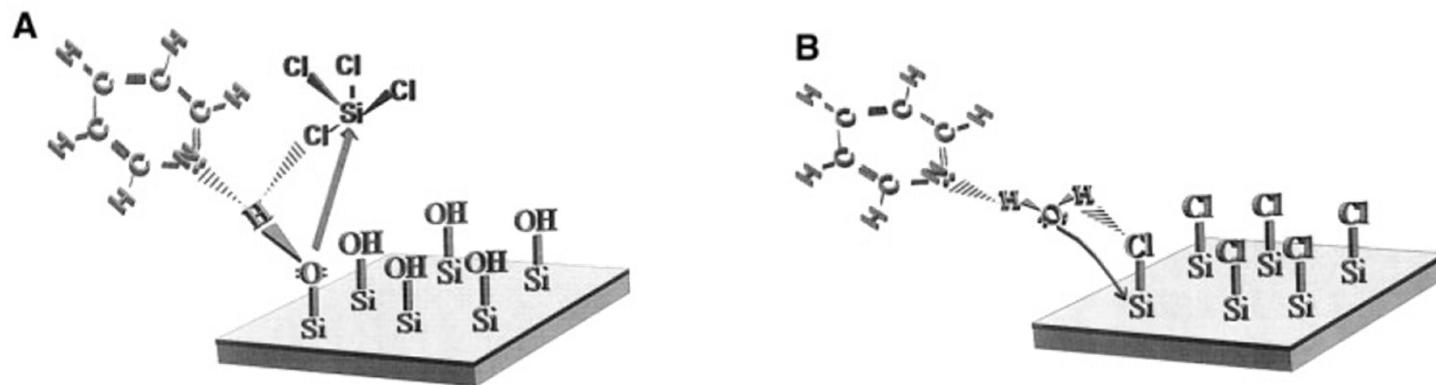
Beyond A/B/A/B... - New Processes

Growth of SiO_2 at Room Temperature with the Use of Catalyzed Sequential Half-Reactions

Jason W. Klaus, Ofer Sneh,* Steven M. George†

SCIENCE • VOL. 278 • 12 DECEMBER 1997

- A+C/B+C...
- $\text{SiCl}_4(\text{Pyridine})/\text{H}_2\text{O}(\text{Pyridine}) \rightarrow \text{SiO}_2$



Beyond A/B/A/B... - What Else Can We Do?

- 1) Stripe Coating
- 2) Surface Poisoning
- 3) Precursor Synergy
- 4) Nanobowls



1) Stripe Coating

- pattern layers in 3-D, nanoporous materials

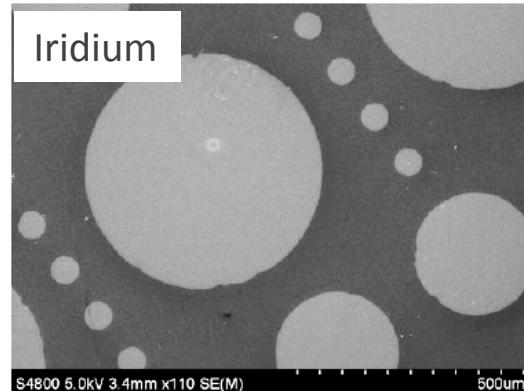
■ Joseph A. Libera

- J. W. Elam, J. A. Libera, P. C. Stair, and M. J. Pellin, Appl. Phys. Lett., **91** 243105-1 – 243105-3, (2007).

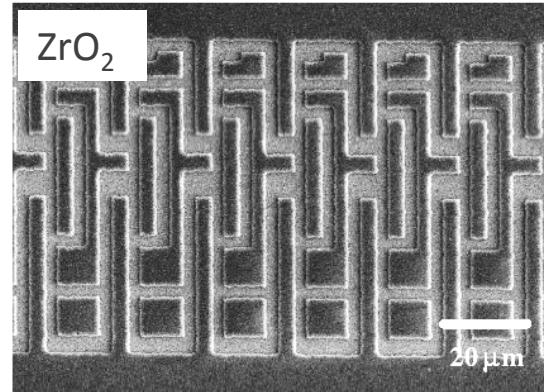


Introduction

- Methods exist for selective ALD on planar surfaces



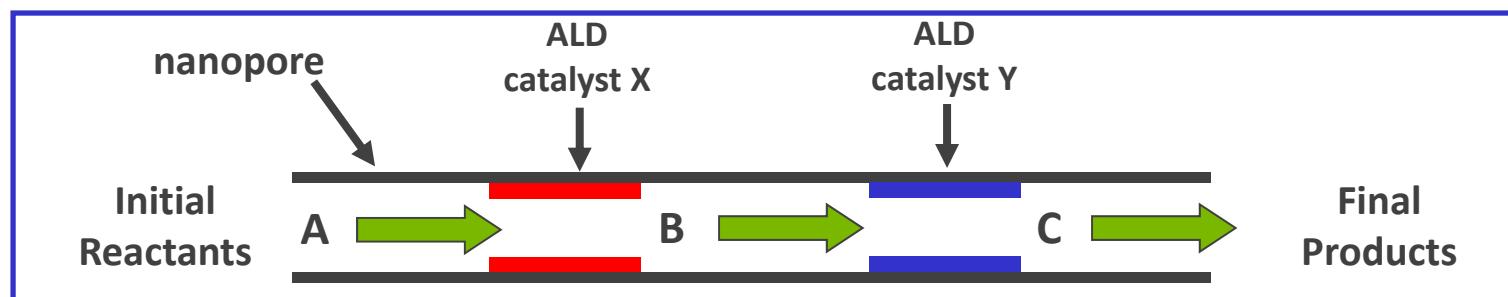
E. Färm et al, CVD 2006, 12, 415–417



J. P. Lee et al, JACS 2004, 126, 28-29

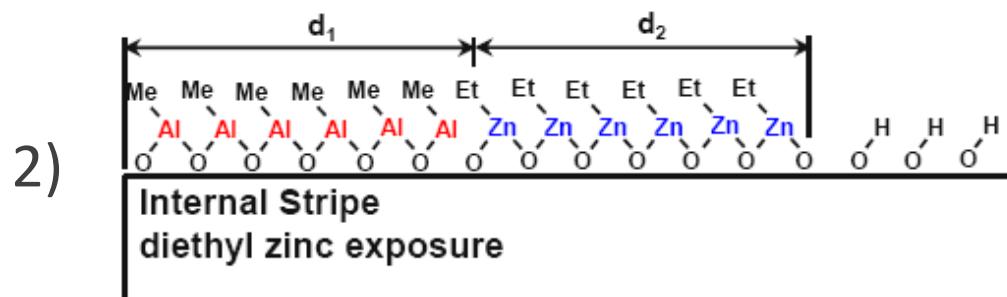
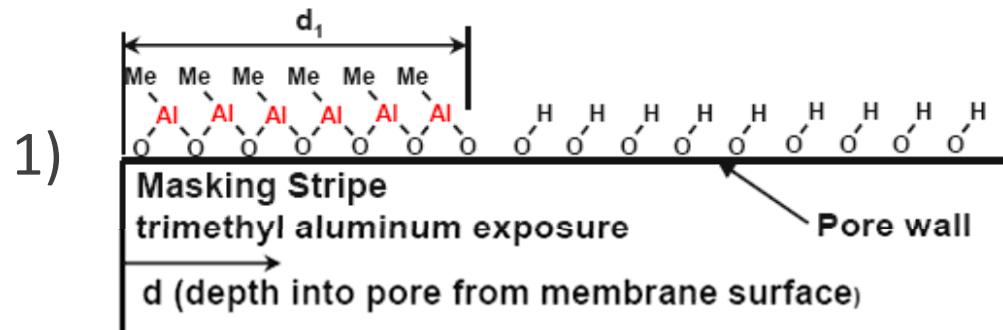
- Can we pattern ALD layers inside of porous structures?

Application - Control of sequential catalytic reactions:



Patterned ALD Layers Inside of Porous Structures

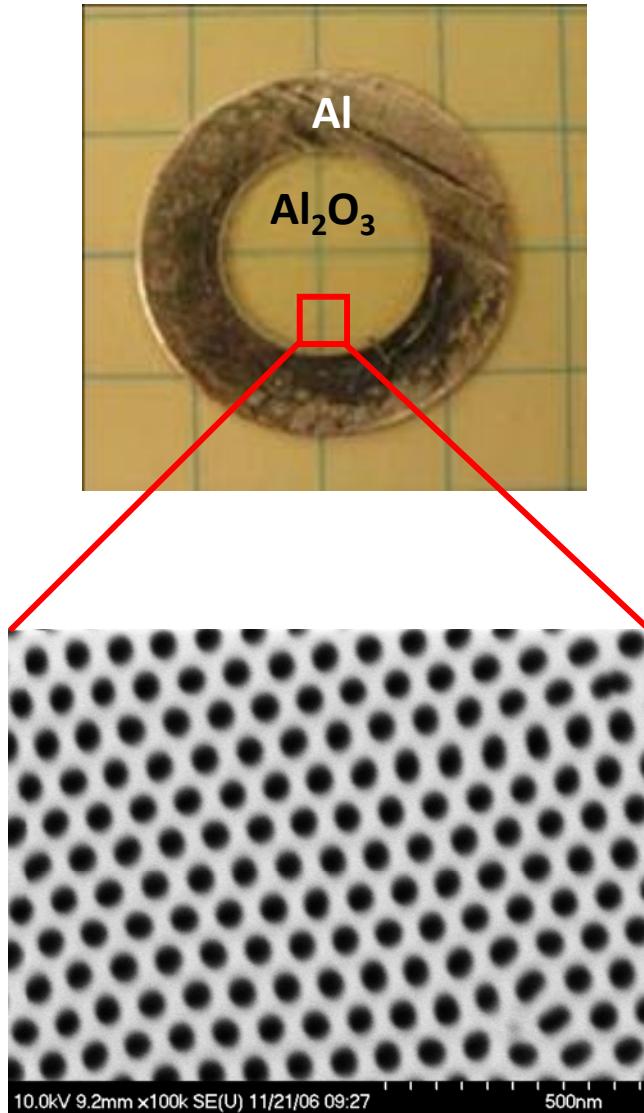
Example: DEZ/H₂O → ZnO



TMA/DEZ/H₂O...
“Stripe Coating”



Anodic Aluminum Oxide (AAO) Membranes



- Electrochemical etching of aluminum metal
- Membrane thickness L=75 μm
- Nanopore diameter d=50 nm
- Aspect ratio L/d = 1400

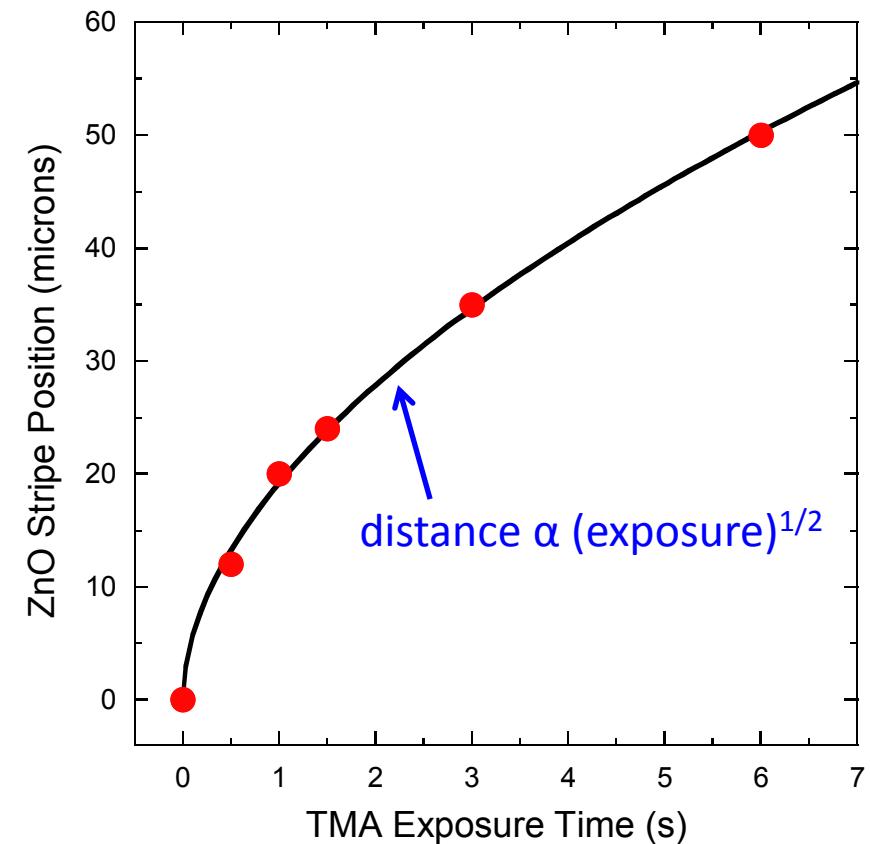
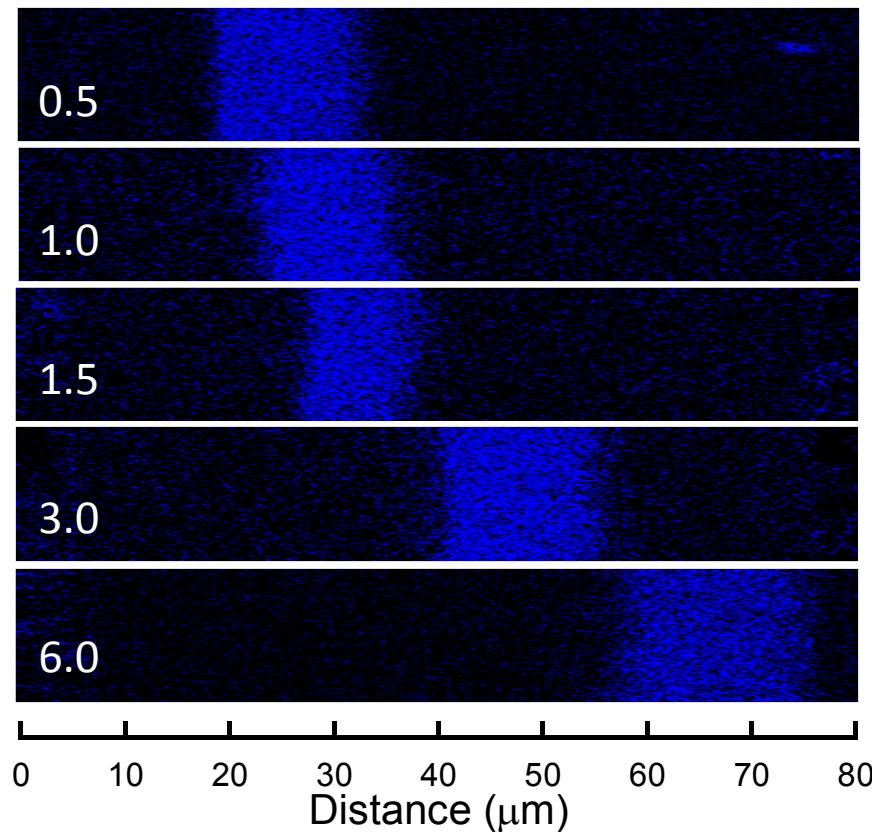


ZnO Stripes in AAO

- 20 cycles TMA-DEZ-H₂O
- Vary TMA exposure time

TMA Exposure

Time:

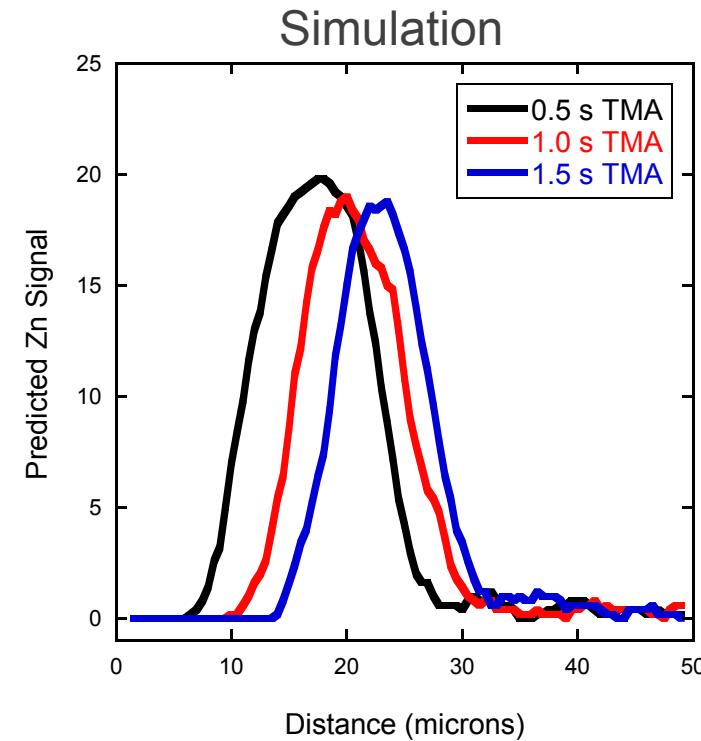
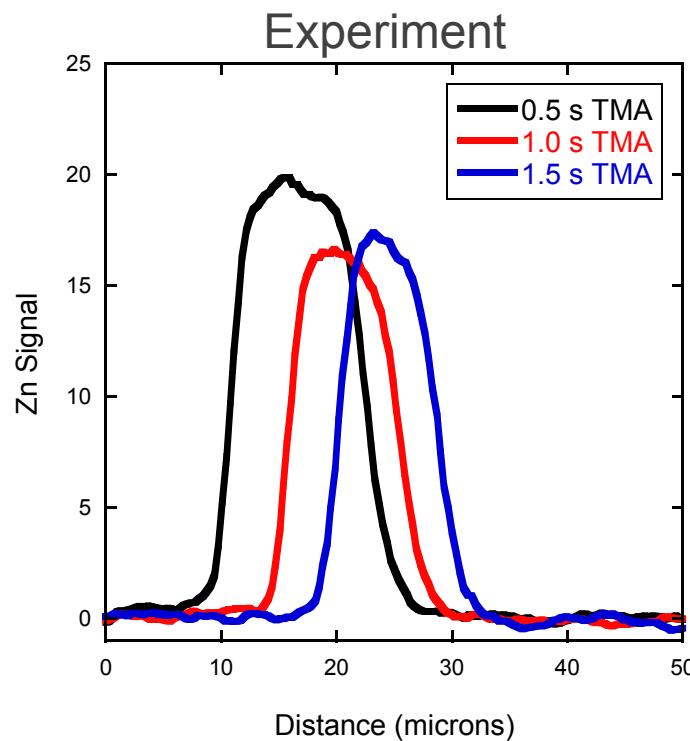


- ZnO stripe position is diffusion-controlled



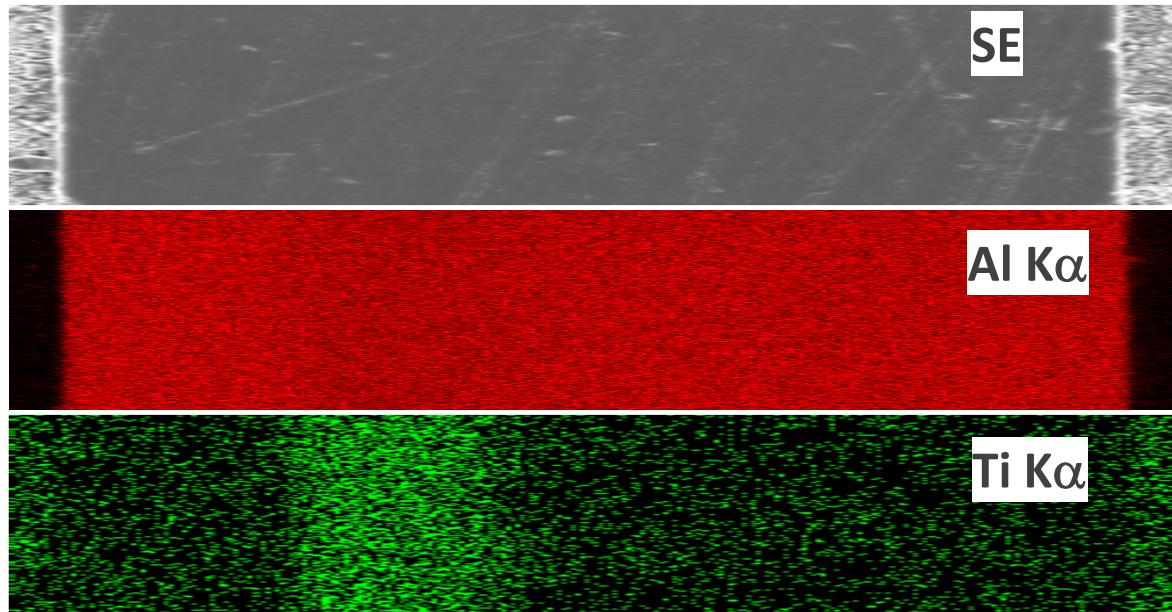
Monte Carlo Simulation of Stripe Coating

- 1D random walk of hop-length d
- Only model DEZ/TMA half-reaction
- Model trajectory until DEZ/TMA reacts ($S=10^{-3}$) or leaves tube



TiO₂ Stripe Coating in AAO

TMA/TiCl₄/H₂O

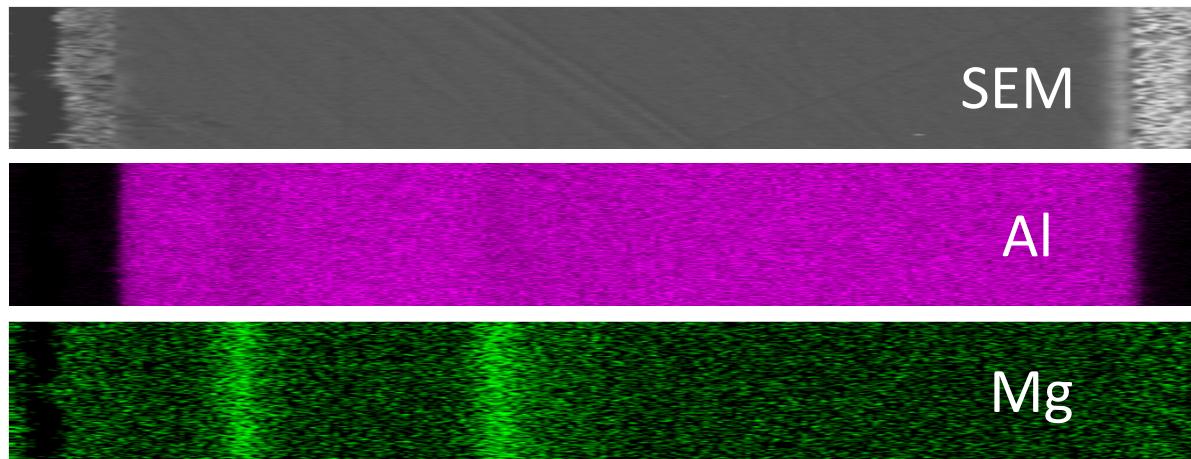


- TiO₂ stripe formed



Multiple Magnesium Oxide Stripes

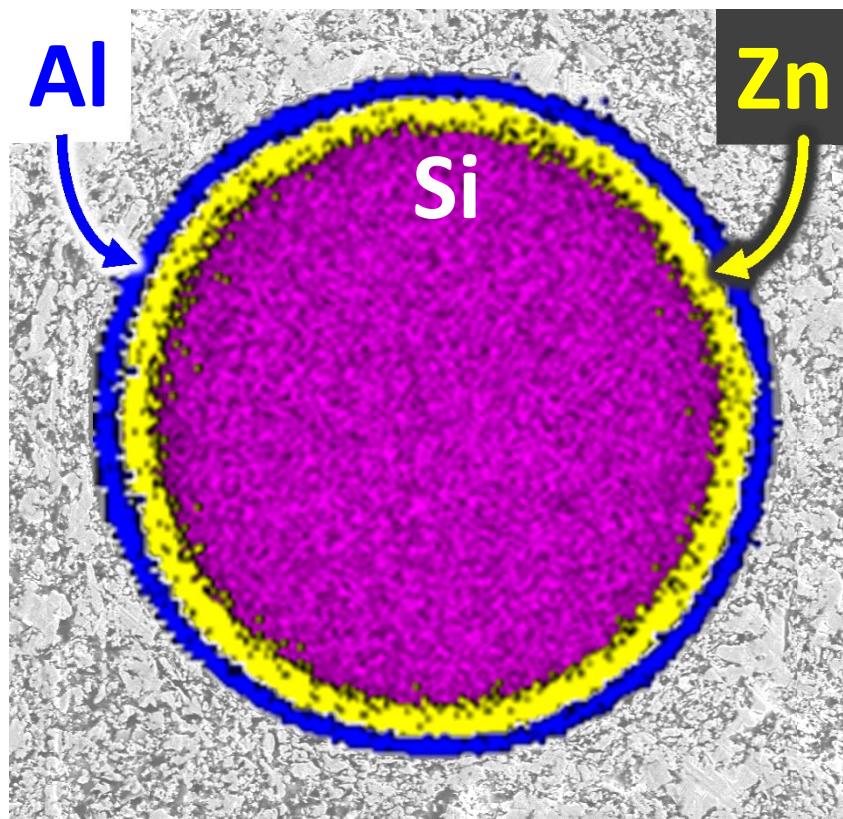
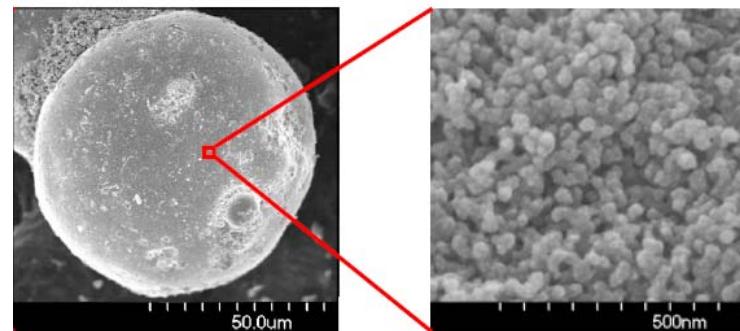
TMA/MgCp₂/TMA/MgCp₂/H₂O



- 2 MgO stripes formed



ZnO Stripe in Silica Gel



- TMA/DEZ/H₂O
- Stripe coating works in other porous media

2) Surface Poisoning

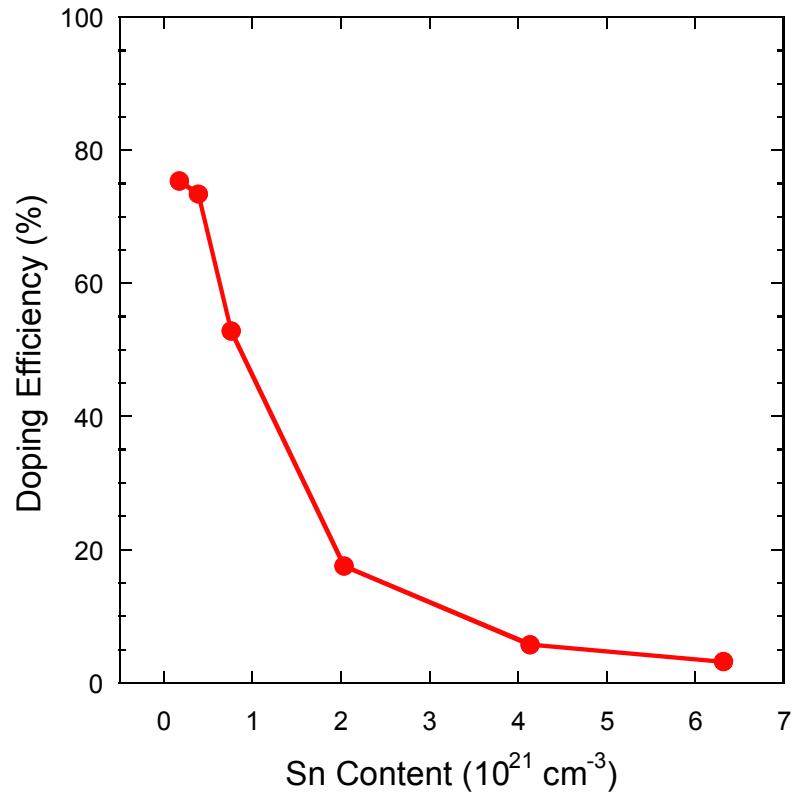
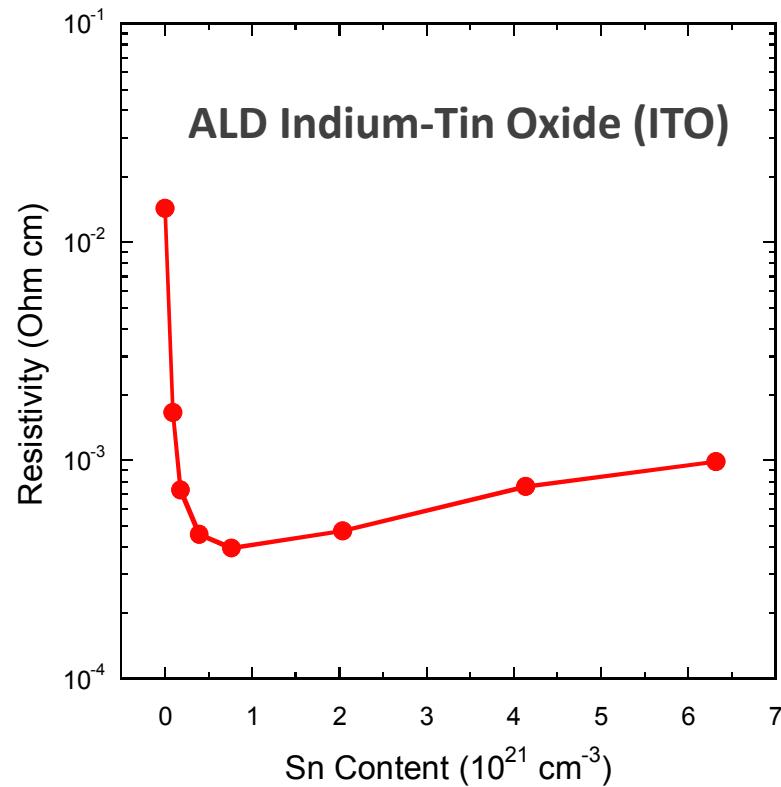
- *control spatial location of dopants in a host*

■ Angel Yanguas-Gil

- A. Yanguas-Gil and J. W. Elam, ECS Trans. **33** (2), 333 (2010).
- A. Yanguas-Gil and J. W. Elam, Chemistry of Materials, **23** (19), 4295-4297, (2011).



What Limits Conductivity in Transparent Conducting Oxides (TCOs)?

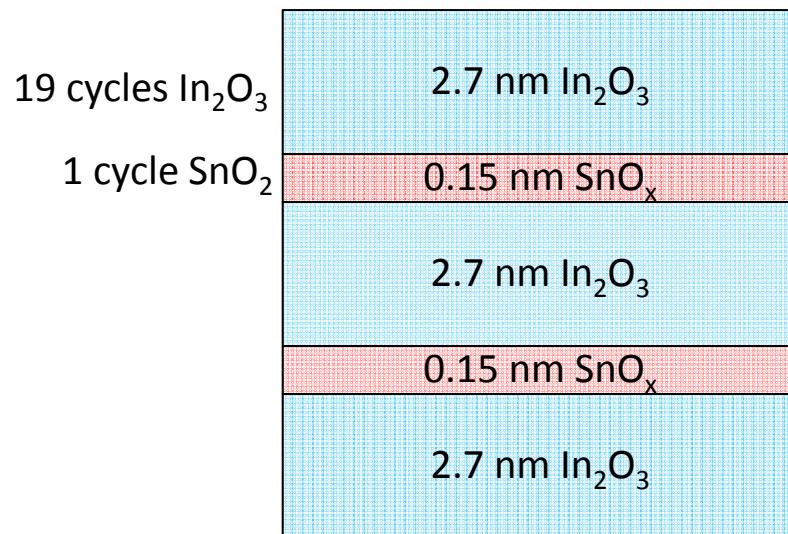


- Doping efficiency decreases with increasing Sn content
- Additional Sn forms non-conducting **Sn-O-Sn** clusters
 - Want a more uniform dispersion of SnO_x
 - For ALD TCOs, need a *lower* SnO₂ growth rate



Why lower the ALD dopant growth rate?

5% ALD ITO:

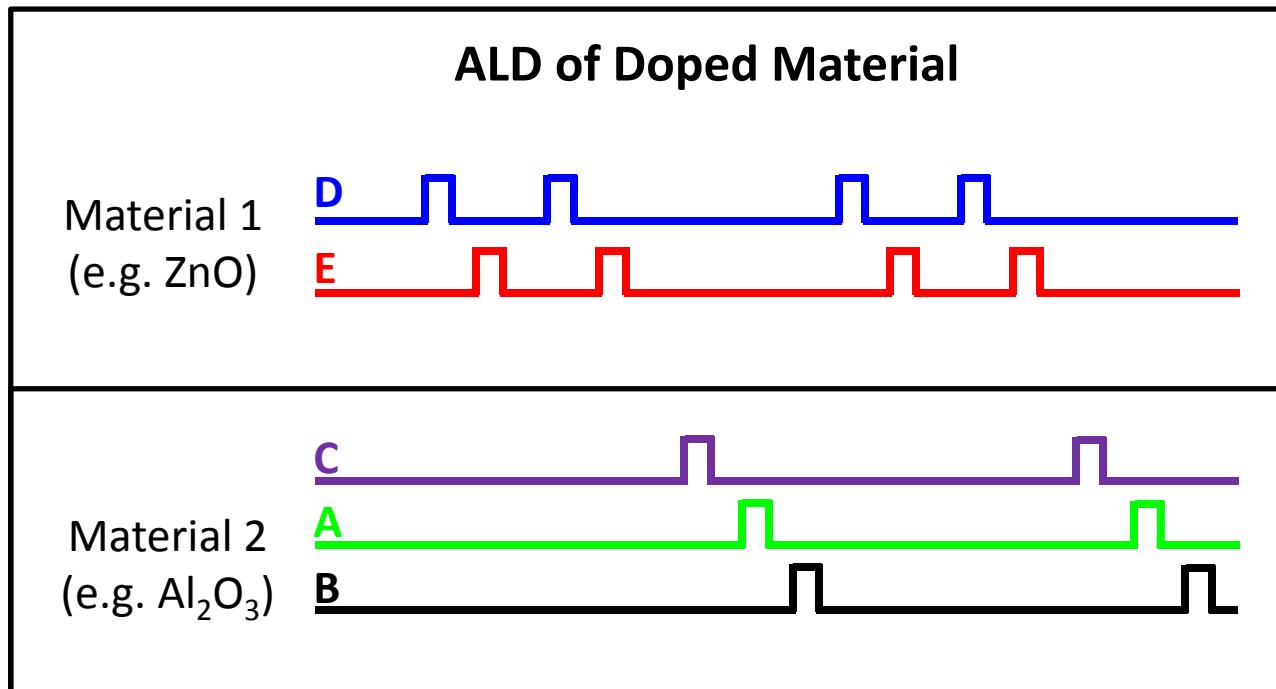


Achieve a more uniform SnO_x dispersion

How? - surface poisoning



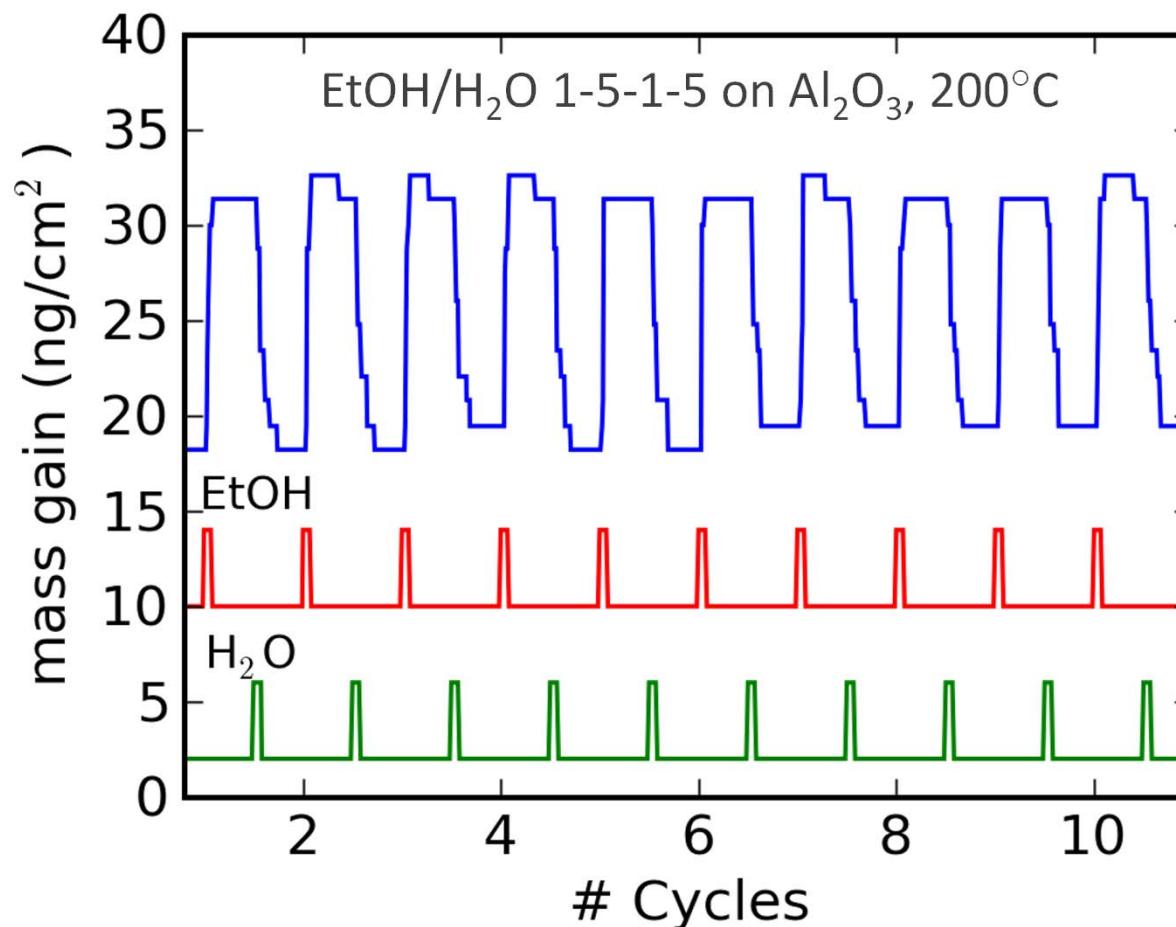
Strategy: Surface Poisoning



- Growth rate *modulated* by poisoning step
- Initially focus on single-component material: Al₂O₃
- Use alkyl alcohols (ROH) as poison



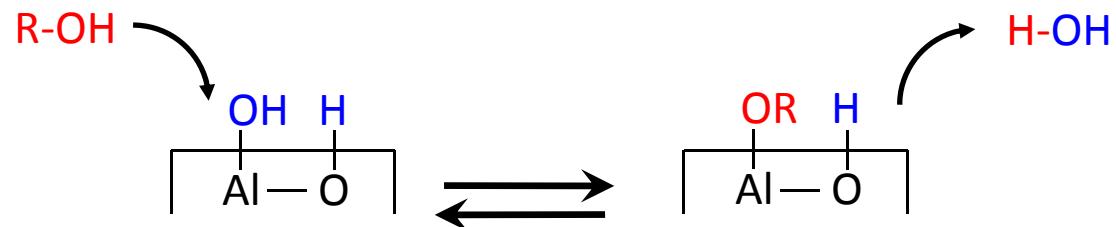
QCM Measurements of EtOH/H₂O on Al₂O₃



- H₂O displaces EtOH
- EtOH displaces H₂O



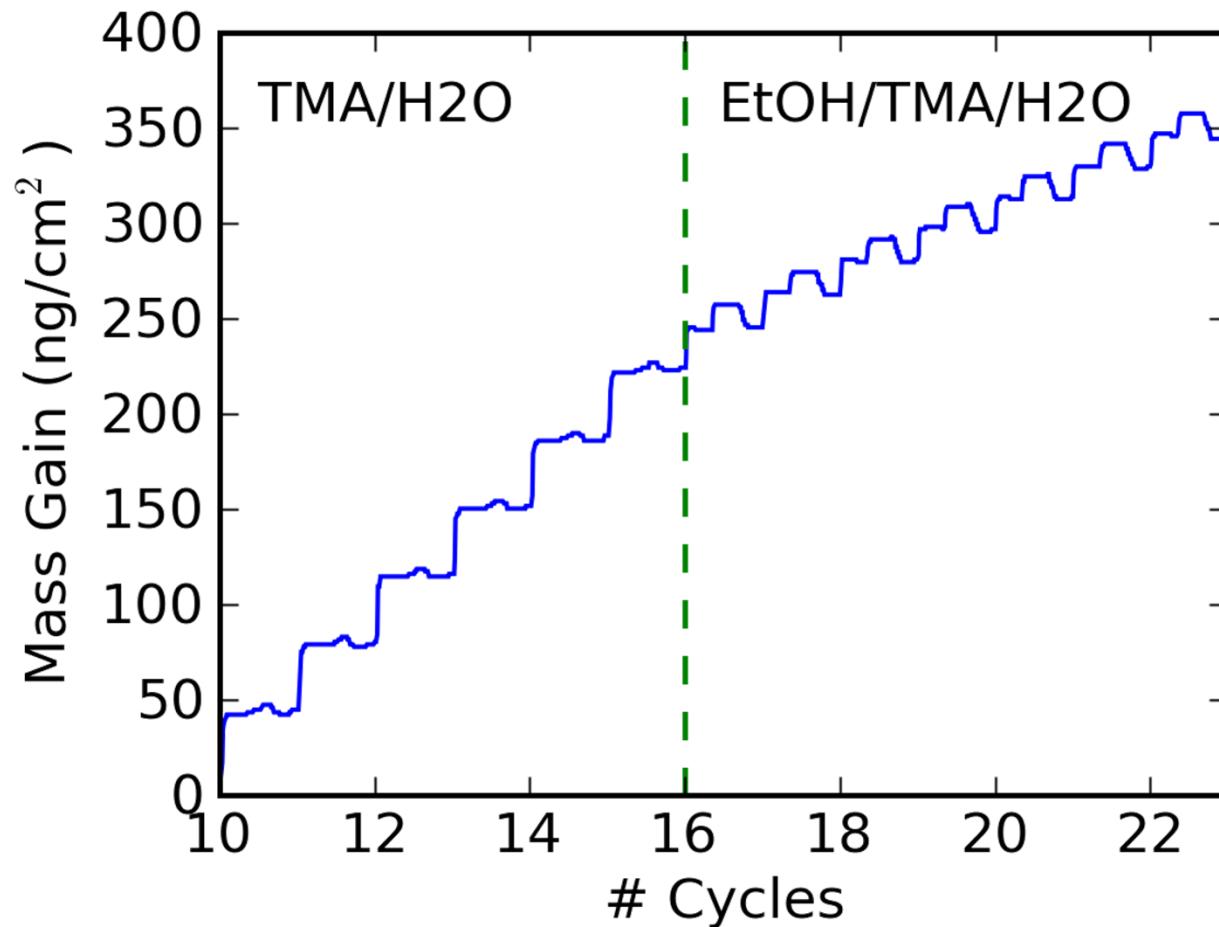
Mechanism for ROH Adsorption on Al₂O₃



J. Phys. Chem. 1996, 100, 18183



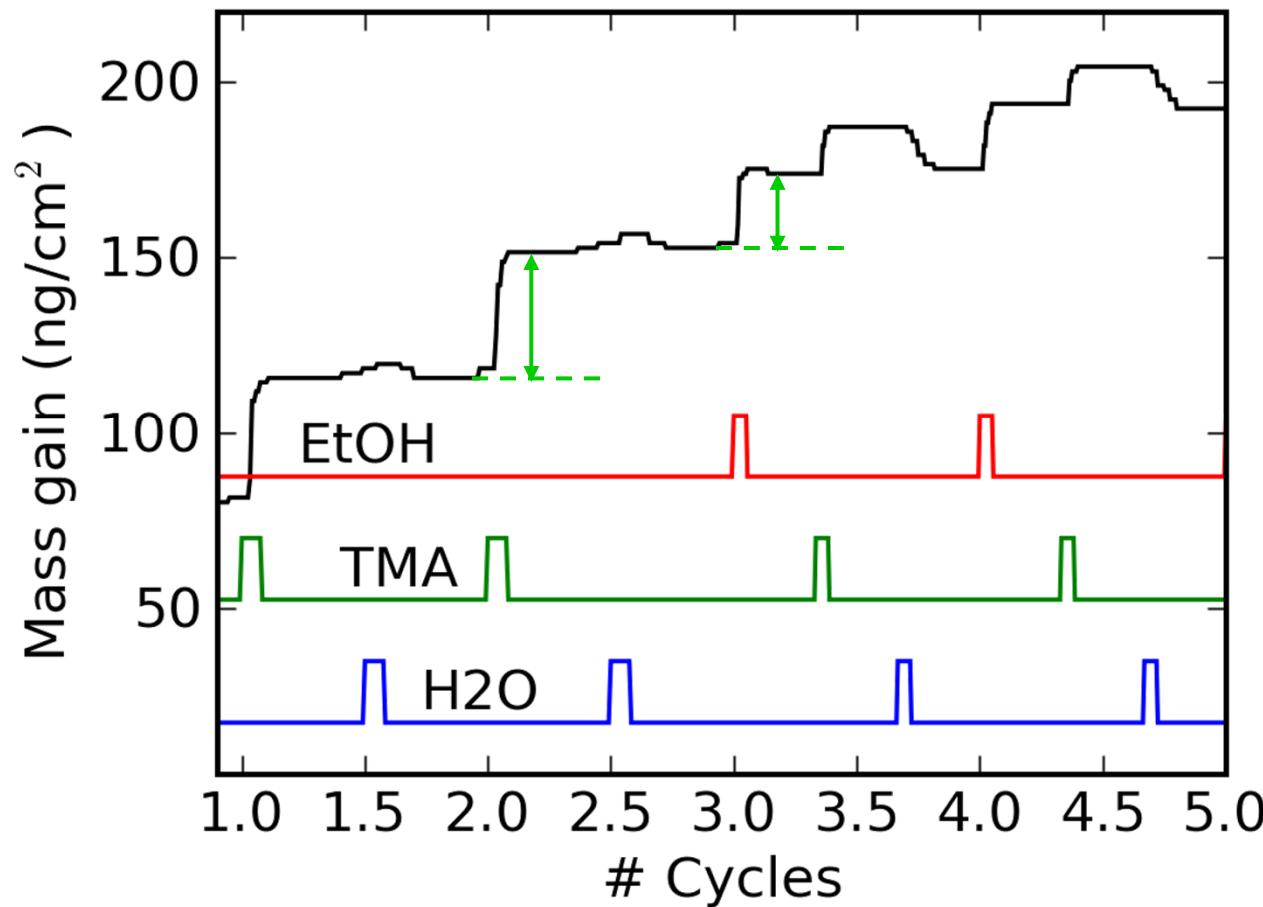
QCM of Al_2O_3 ALD Using EtOH/TMA/H₂O



- Al_2O_3 grows more slowly with the EtOH



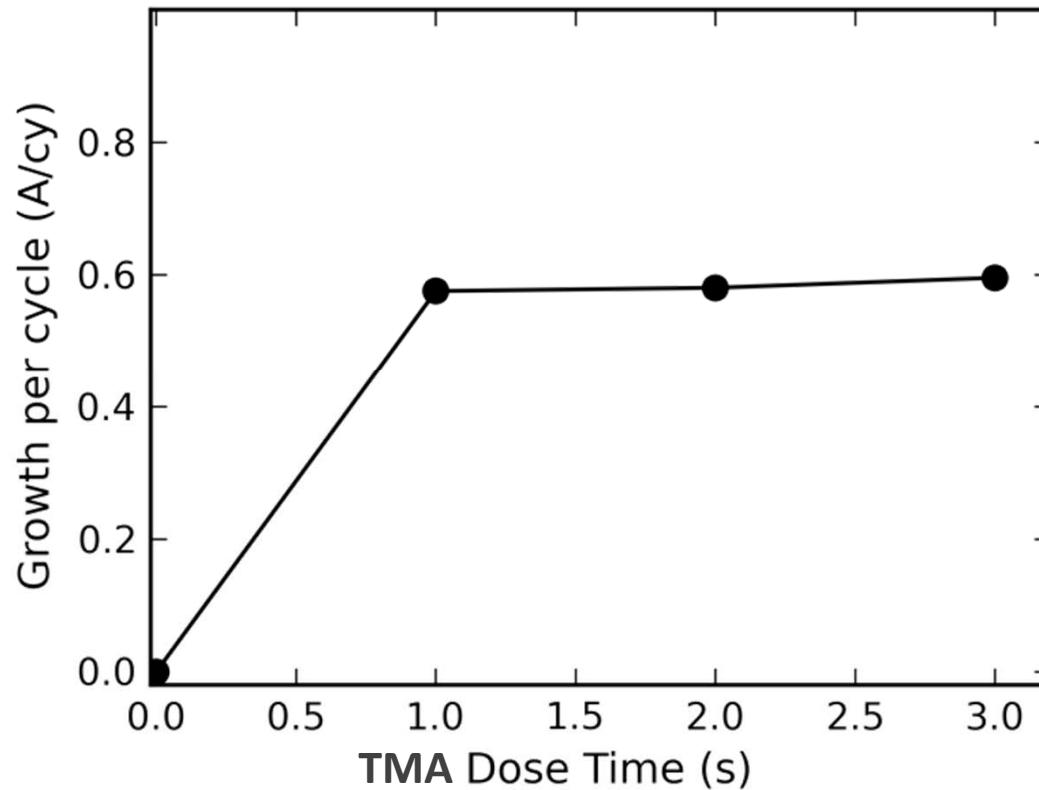
QCM Pulse Structure During EtOH/TMA/H₂O



- Mass is gained during TMA exposures
- This mass gain is *smaller* following EtOH



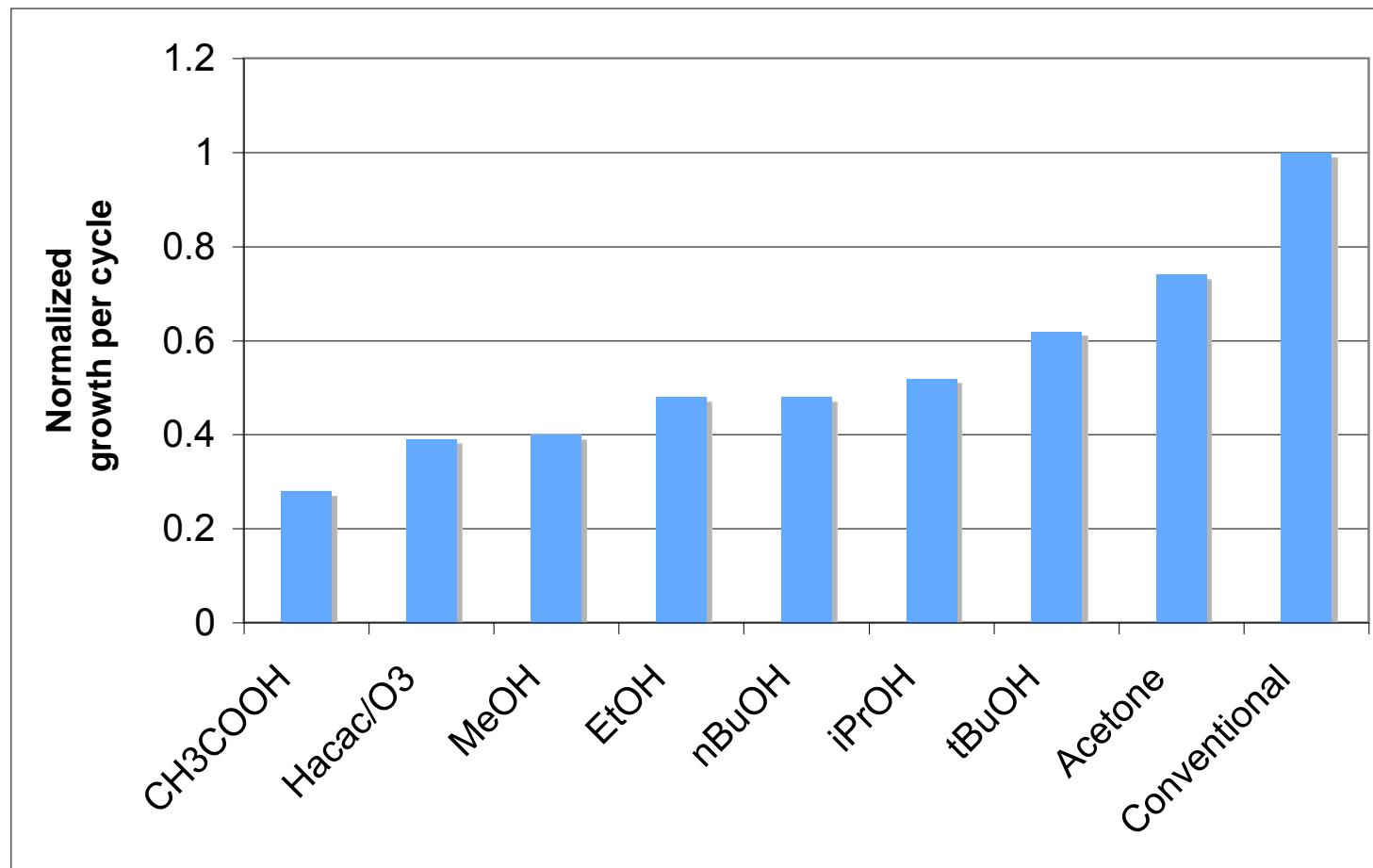
Self-limiting TMA Reaction During EtOH/TMA/H₂O



- EtOH/TMA/H₂O is self-limiting
- No growth from EtOH/TMA
- Nominal growth from EtOH/H₂O/TMA/H₂O



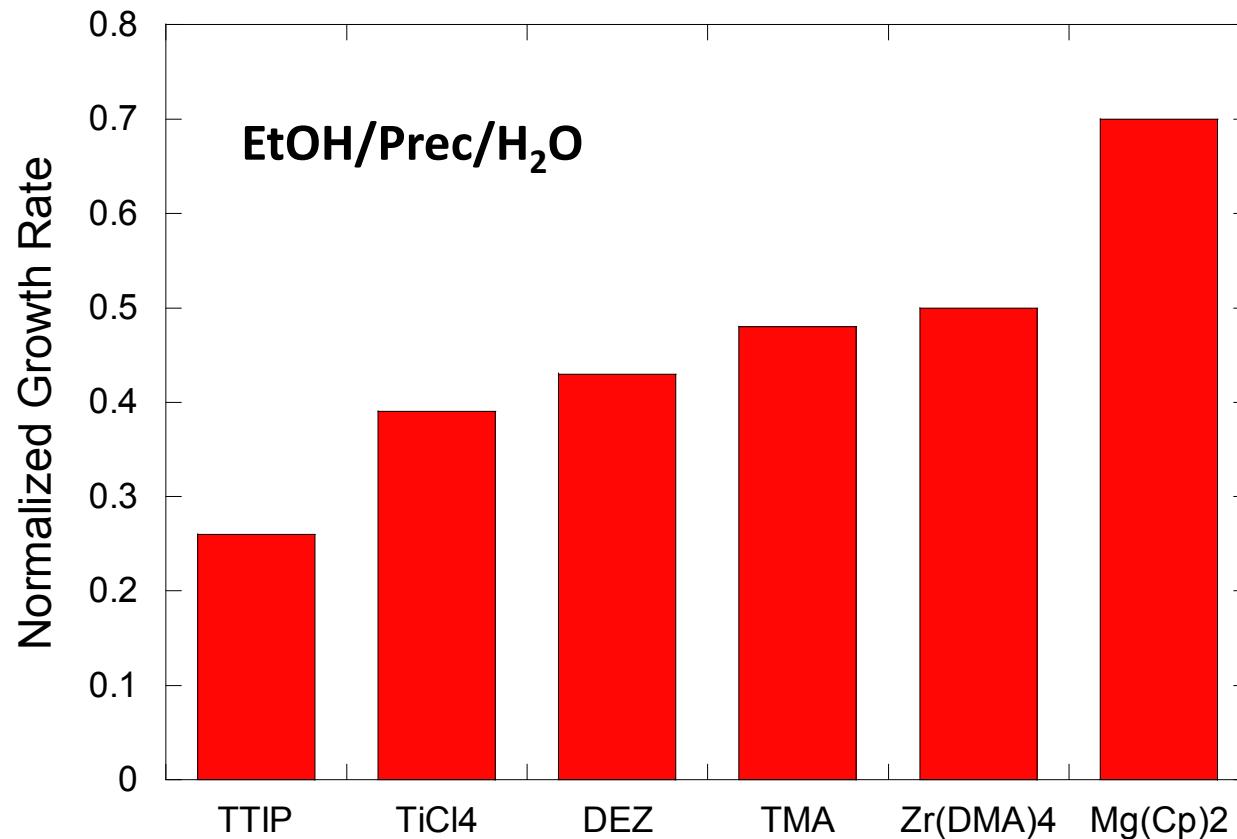
Summary of Surface Poisoning Using TMA



- Many organic compounds act as growth inhibitors
- Wide range of Al₂O₃ ALD growth rates



Growth Modulation for Other Precursors

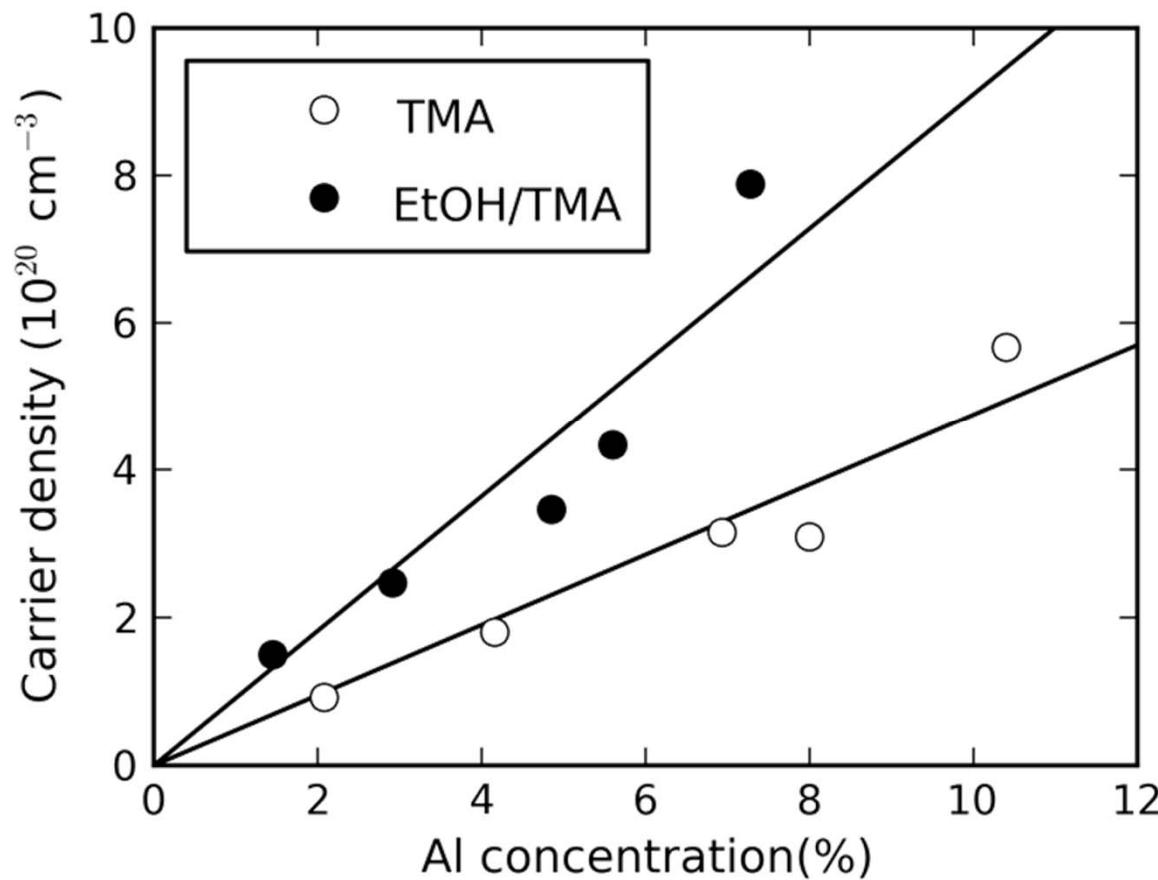


- Surface poisoning works with many ALD materials



Application: Aluminum-Doped ZnO

- Al:ZnO with and without EtOH poisoning
- Measure doping efficiency



- 2x higher doping efficiency with surface poisoning



3) Precursor Synergy

- *make precursors cooperate*

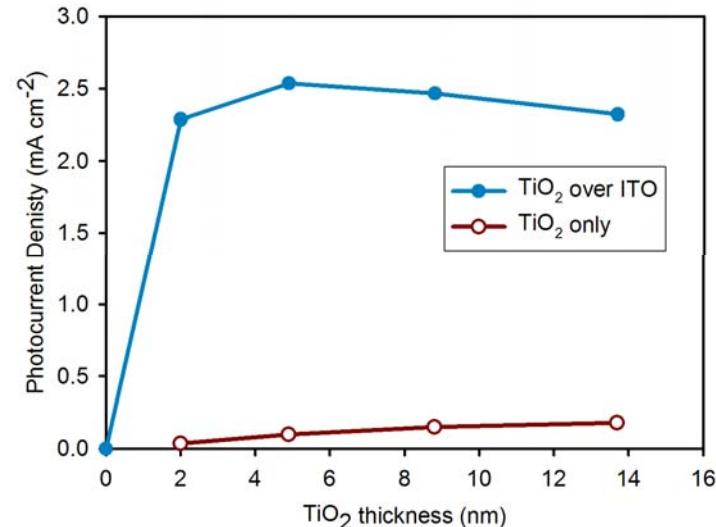
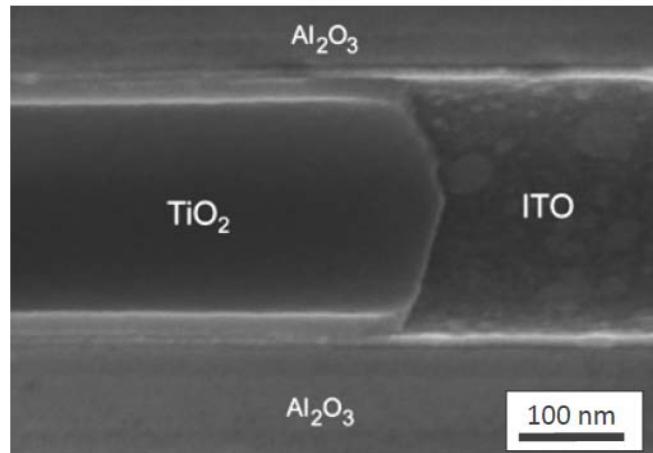
■ Joseph A. Libera

- J. A. Libera, J. N. Hryn, and J. W. Elam, Chemistry of Materials (2011).



In_2O_3 ALD using Ozone

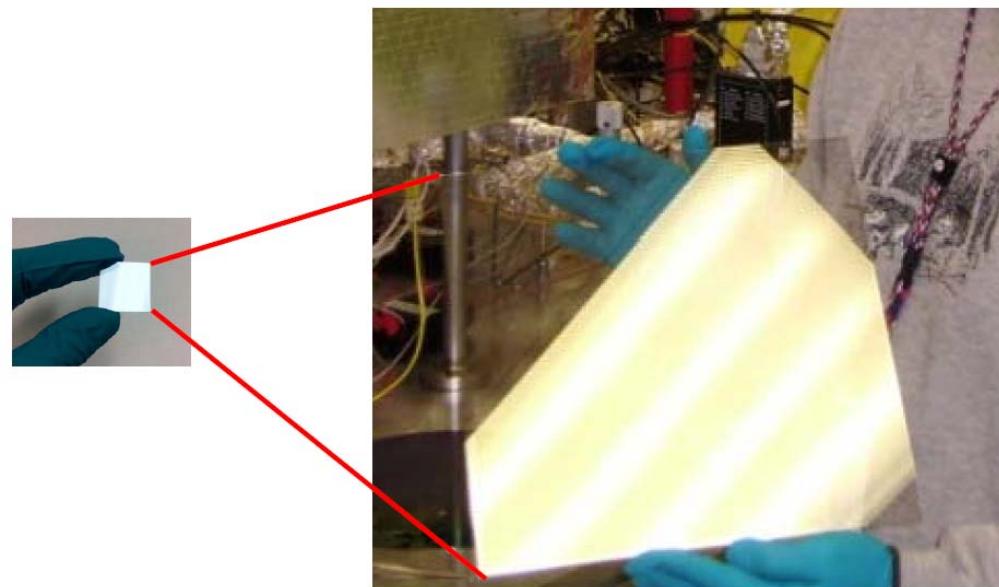
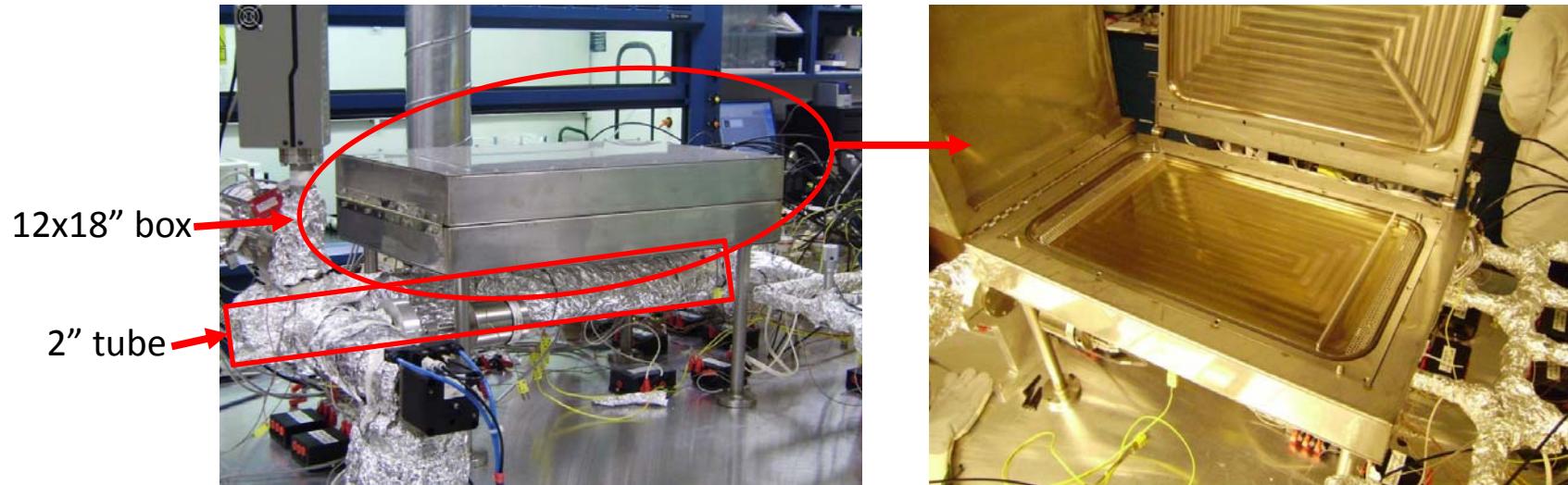
ALD ITO in nanopores (AR=300) for solar cells:



- $\text{InCp} + \text{O}_3 \rightarrow \text{In}_2\text{O}_3 \quad (\text{In}^{+1} \rightarrow \text{In}^{+3})$
- In_2O_3 films were thinner downstream in reactor
- $\text{O}_3 \xrightarrow{\text{In}_2\text{O}_3} \text{O}^* + \text{O}_2$
- Indium oxide catalyzes ozone destruction

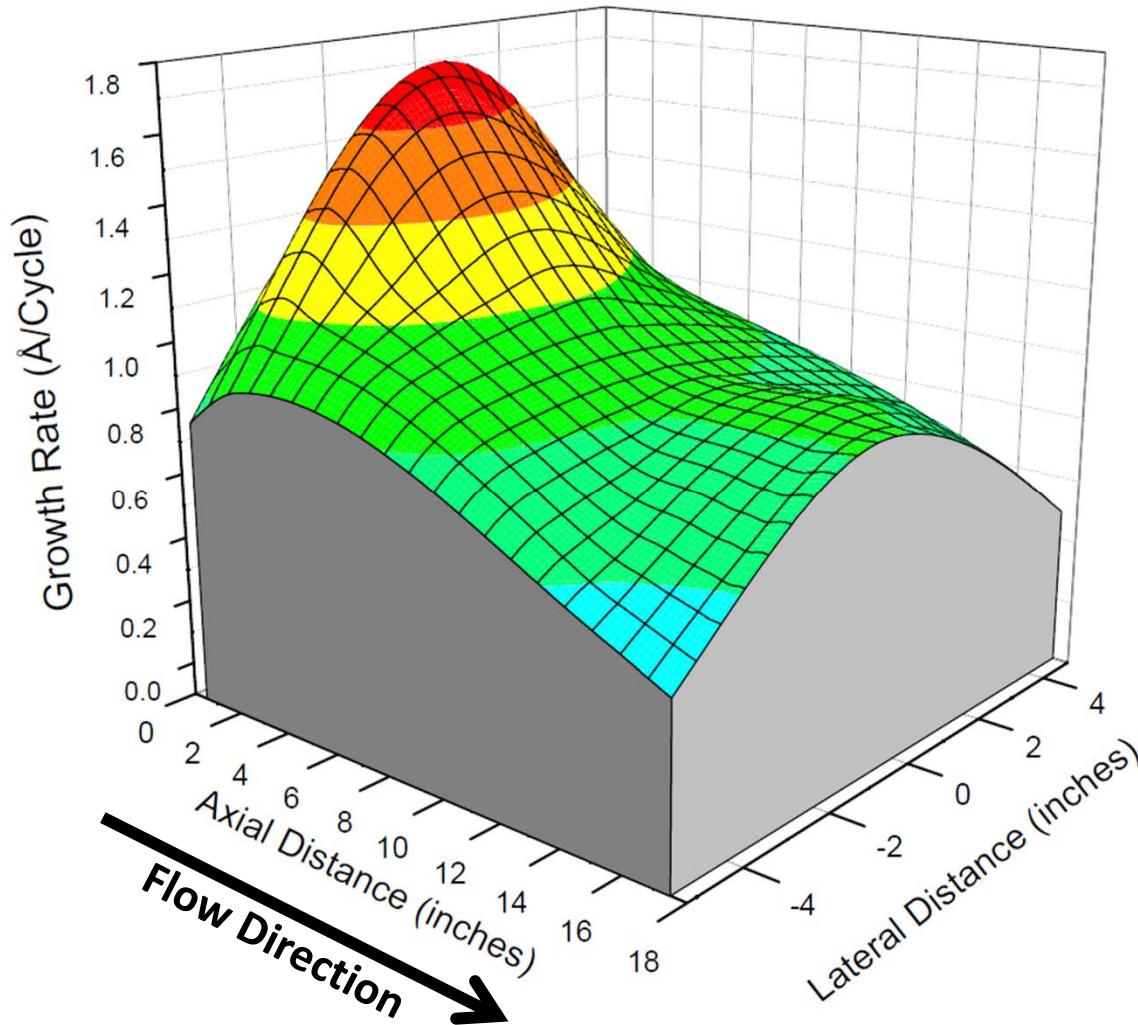


Scale-up of ALD ITO using Large Substrate Reactor



- From 1x1-in plates to 12-in x 18-in plates

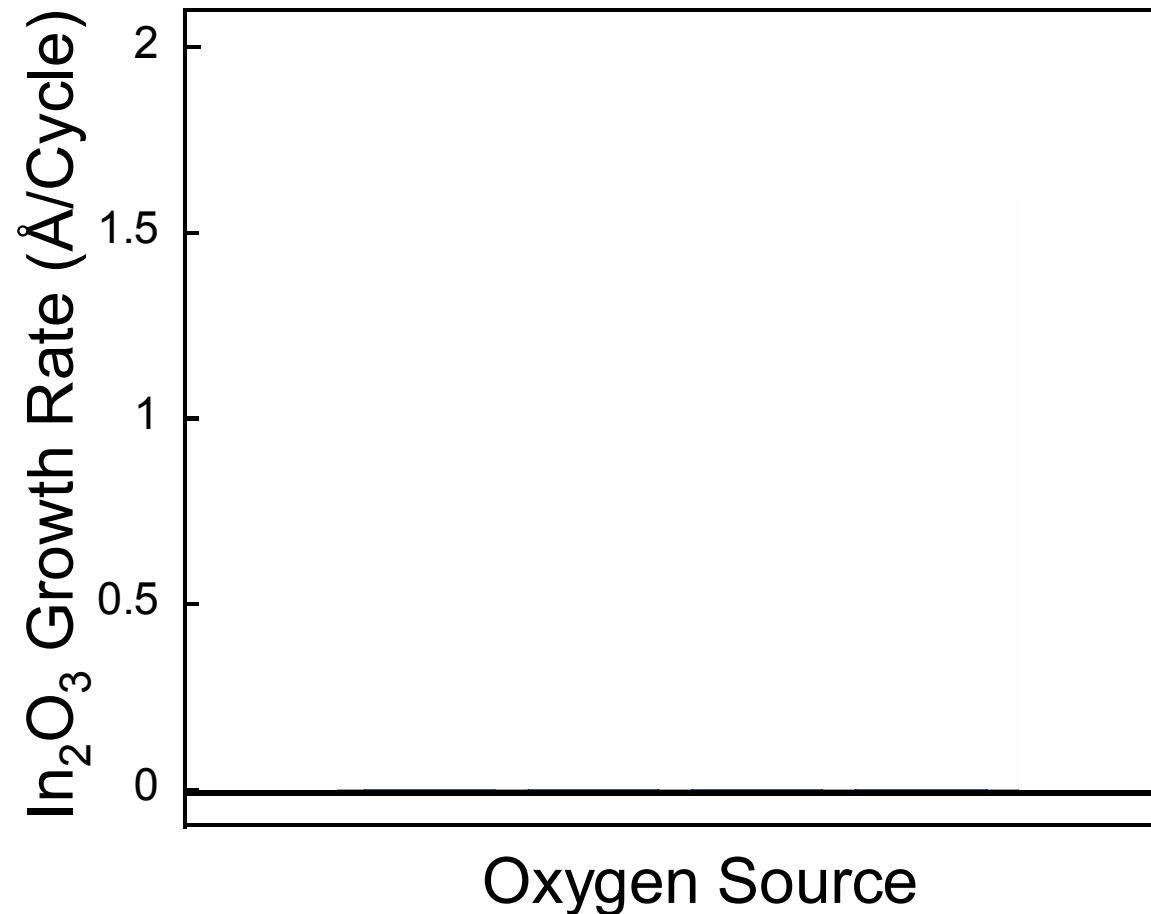
Spatial Uniformity of ALD ITO Using InCp/O₃



- Very poor uniformity ($\pm 45\%$)
- In₂O₃-catalyzed decomposition of O₃
- Can we develop an ALD process that does not require O₃ ?...



Different Oxygen Sources for In_2O_3 ALD with InCp

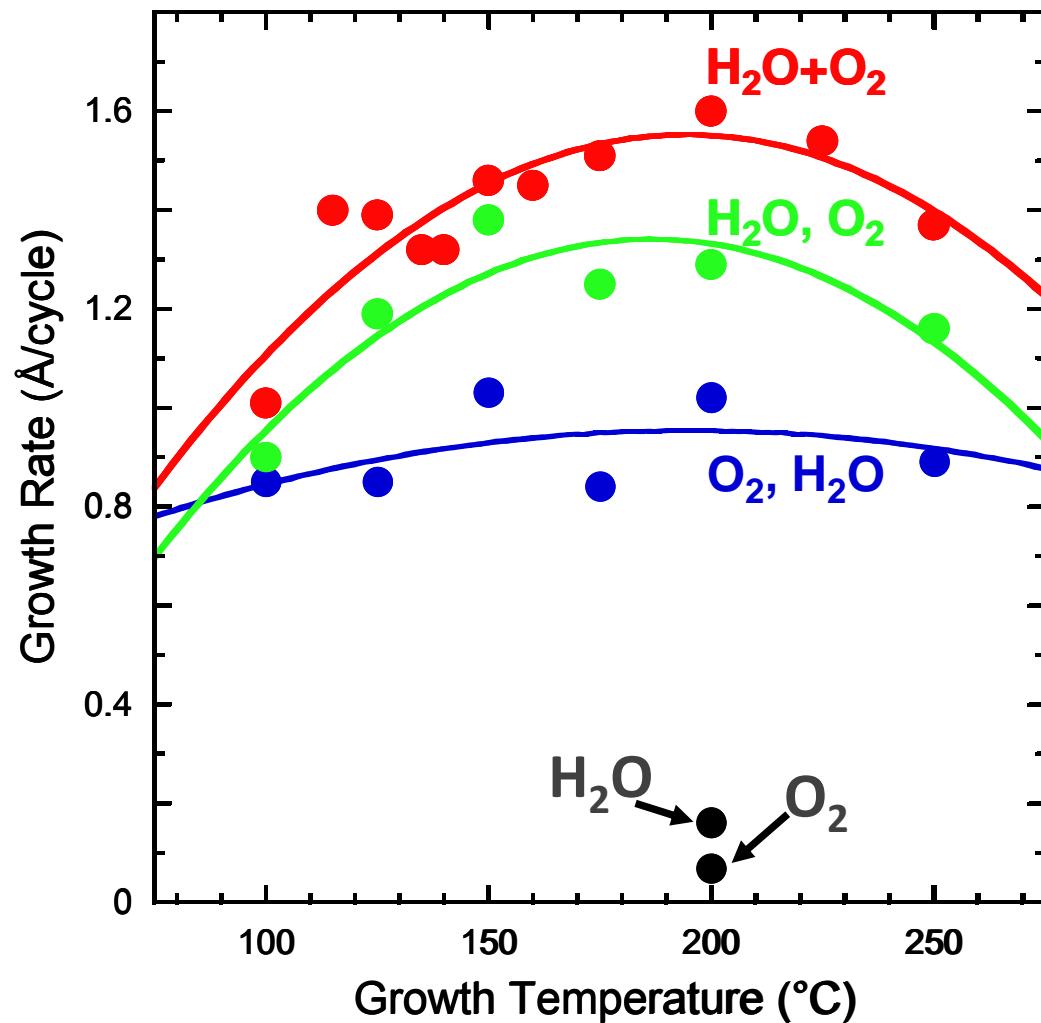


- In_2O_3 ALD does not work with either O₂ or H₂O alone
- *Simultaneously* dosing O₂ and H₂O allows In_2O_3 ALD



Growth of ALD In_2O_3 using InCp/ $(\text{H}_2\text{O}+\text{O}_2)$

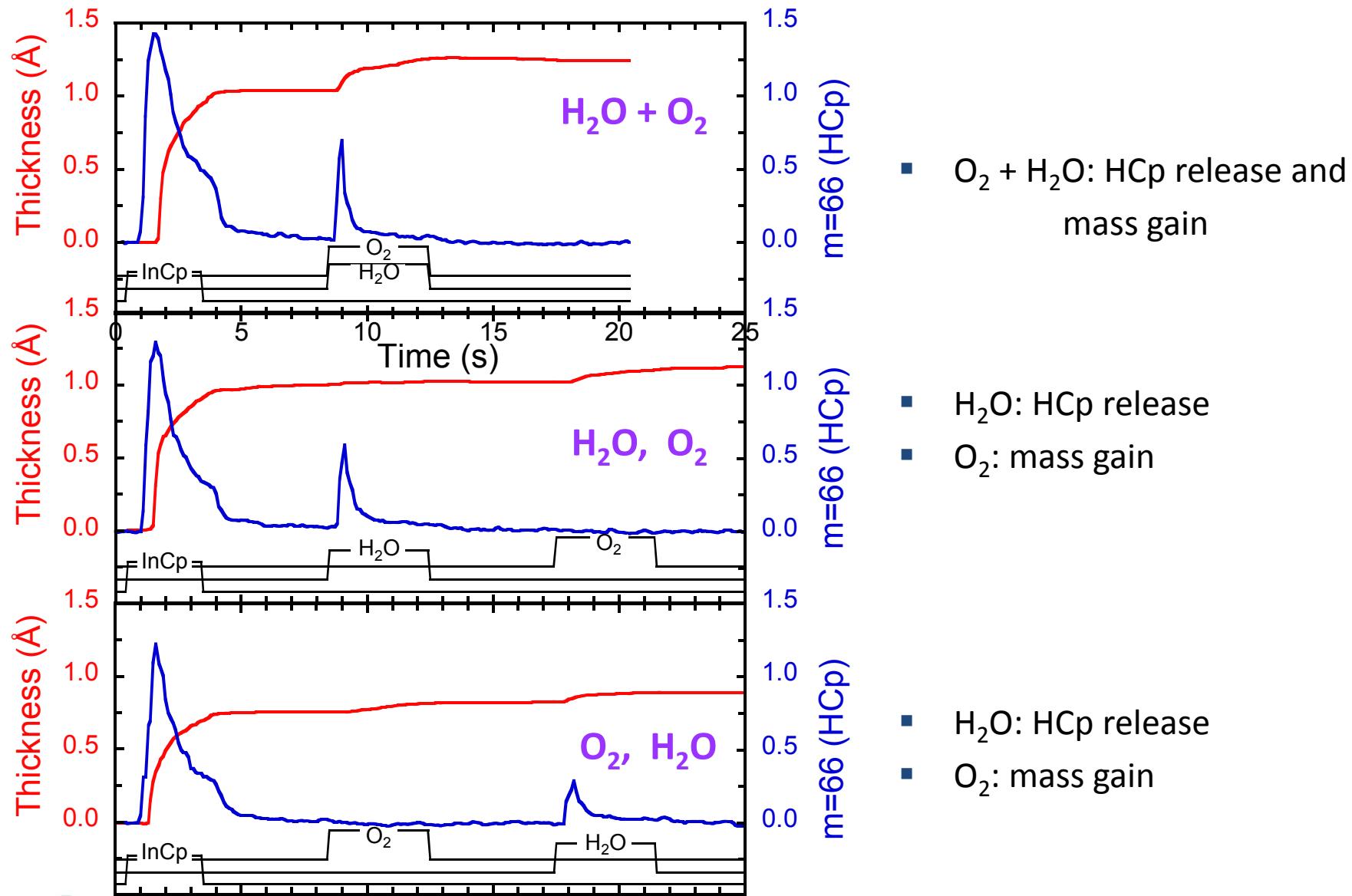
300 cycles on Si(100)
thickness measured by ellipsometry



- High growth rates, $1.0\text{-}1.6 \text{\AA}/\text{cycle}$
- H_2O and O_2 can be supplied simultaneously or in sequence
- Order is not critical
- What is the mechanism?
- Why are *both* H_2O and O_2 required?

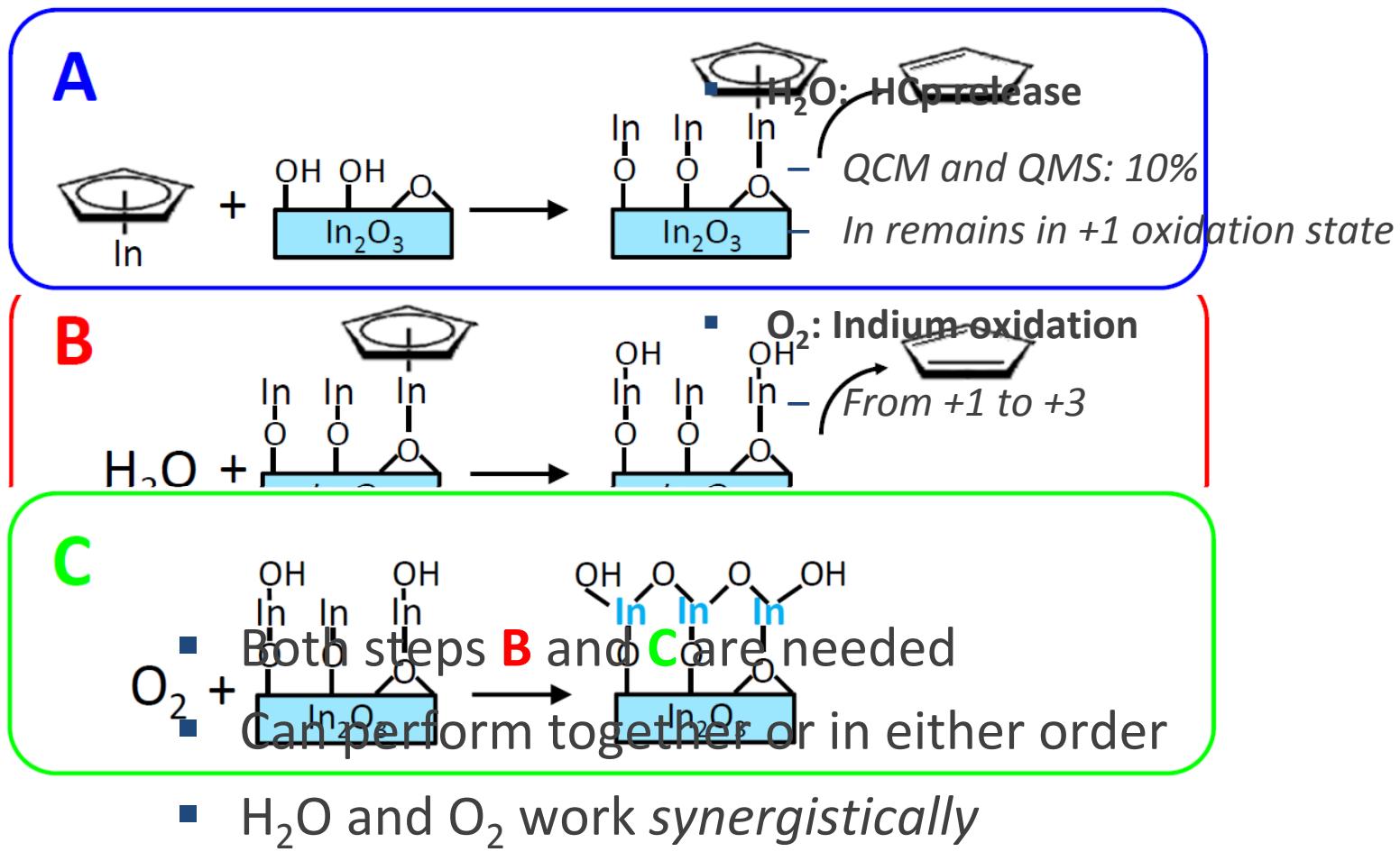


In Situ QCM and QMS During In_2O_3 ALD

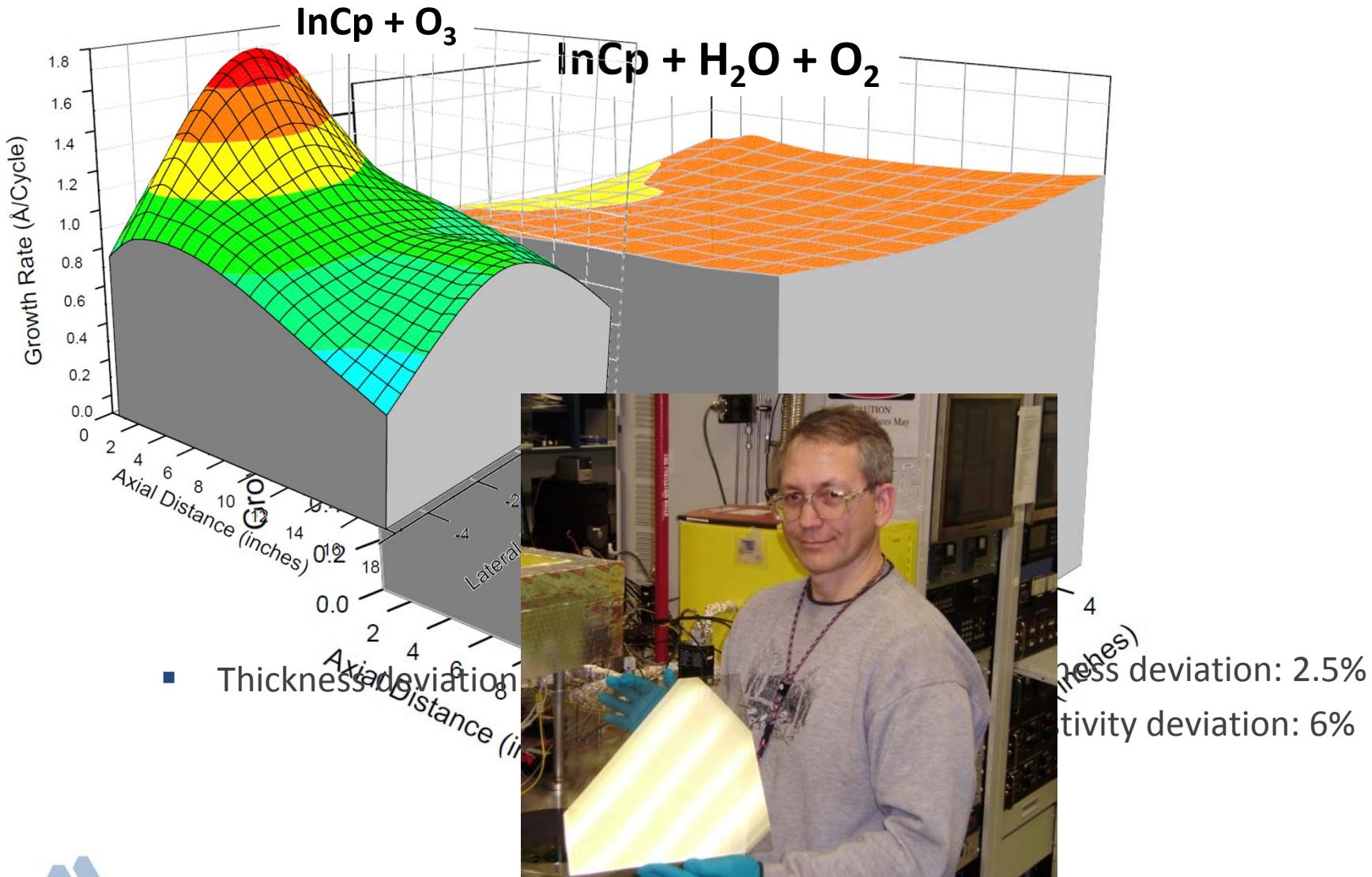


Proposed Mechanism for In_2O_3 ALD

- InCp: HCp release
 - QCM and QMS: 90%



Scale-up of ALD In_2O_3 to 12" x 18" Substrates



4) Nanobowls

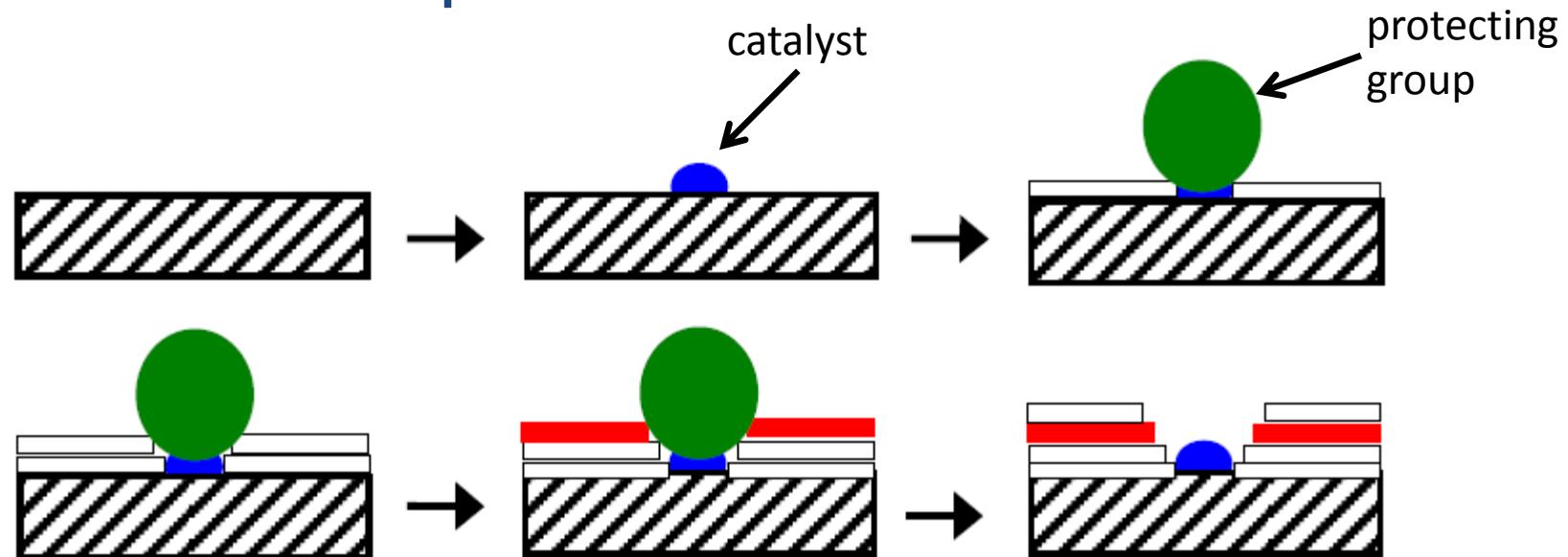
- engineer catalytic environments

- Junling Lu
- Christian Canlas

- J. Lu et. al., Science, **335**, 1205 (2012).
- C. Canlas et. al., Nature Chemistry **4**, 1030, (2012).



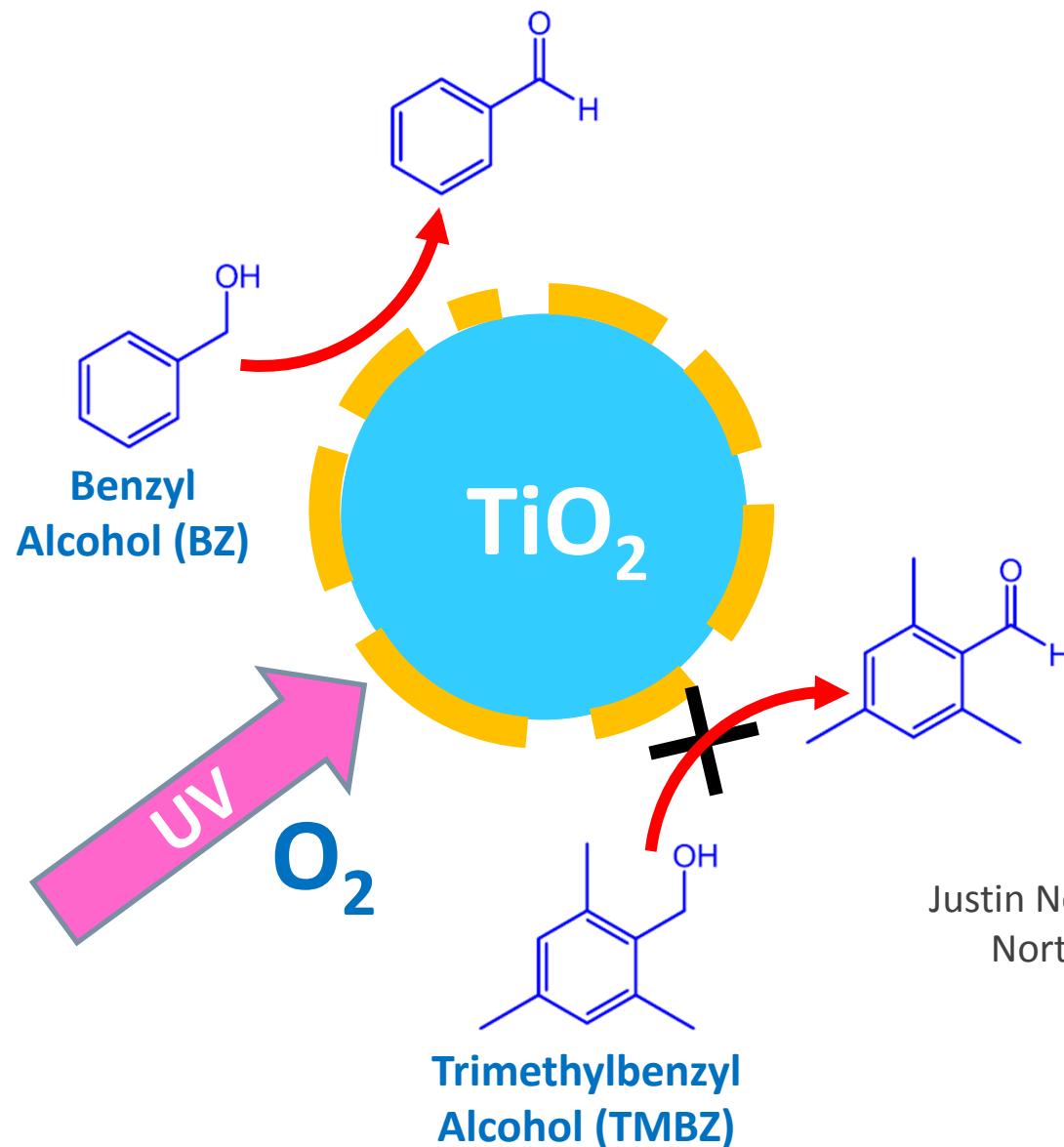
Nanobowl Concept



- Control composition and relative position of multiple catalytic species
- Impart shape-selectivity
- Stabilize catalyst

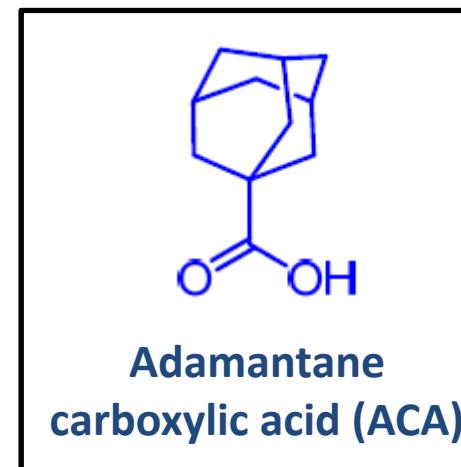
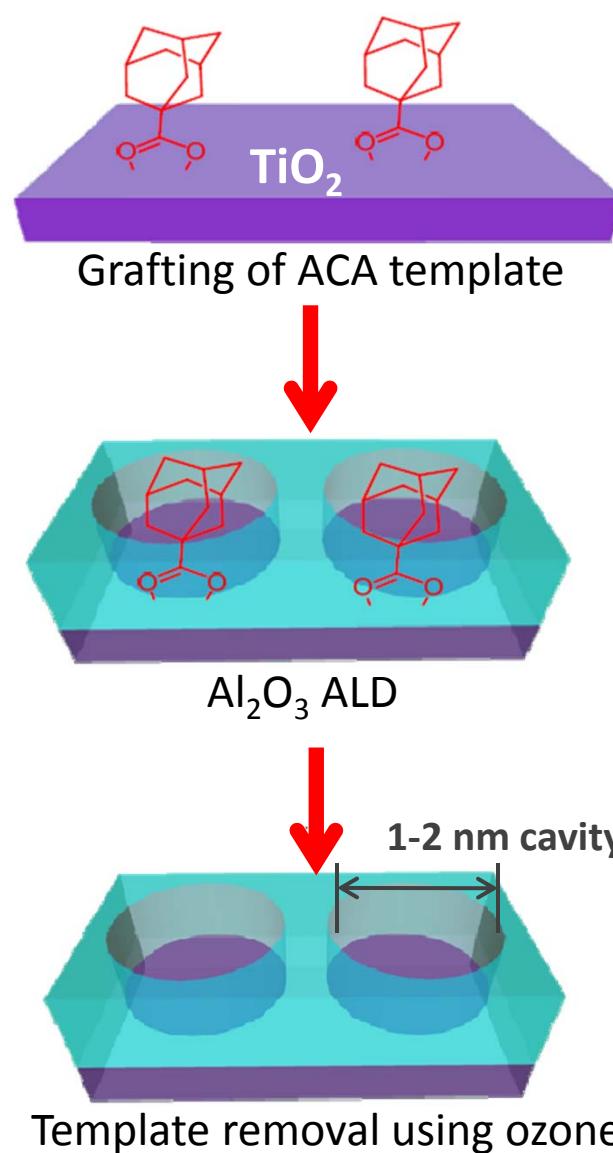


Al_2O_3 Nanobowls on TiO_2 : Shape Selective Photocatalysis

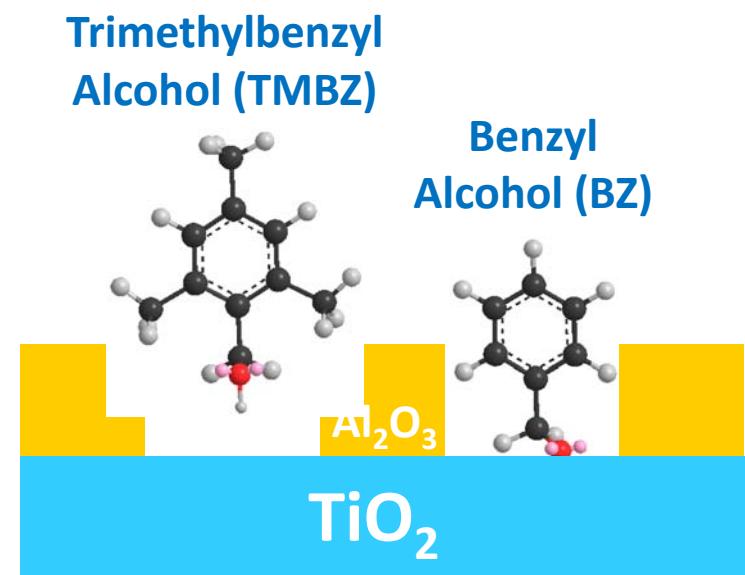
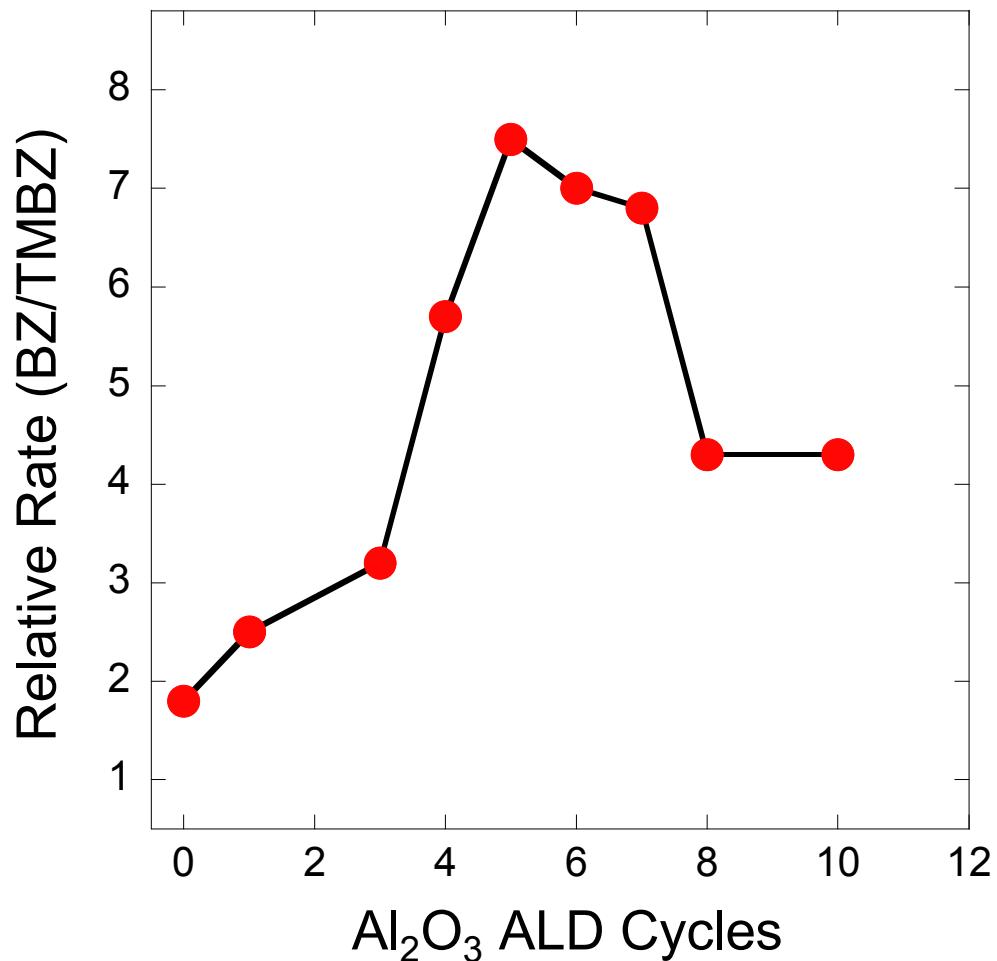


Justin Notstein, Christian Canlas
Northwestern University

Nanobowls on TiO₂ Photocatalyst

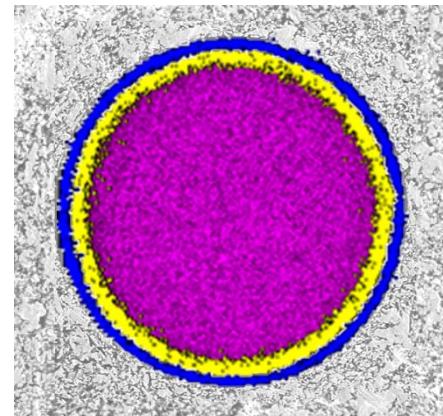


Relative Rates of Photocatalytic Oxidation on Nanobowl Catalysts

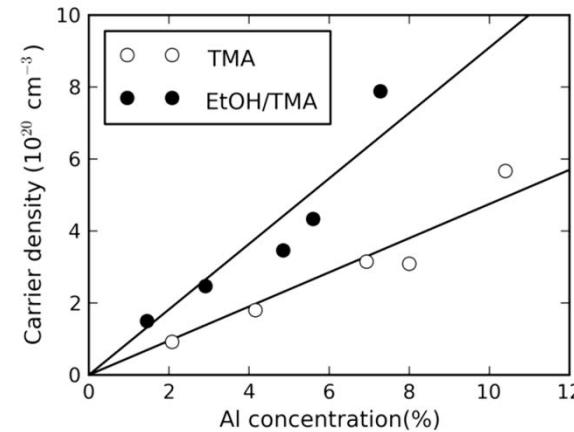


- Remarkable selectivity for BZ after ~ 5 ALD Al_2O_3 Cycles

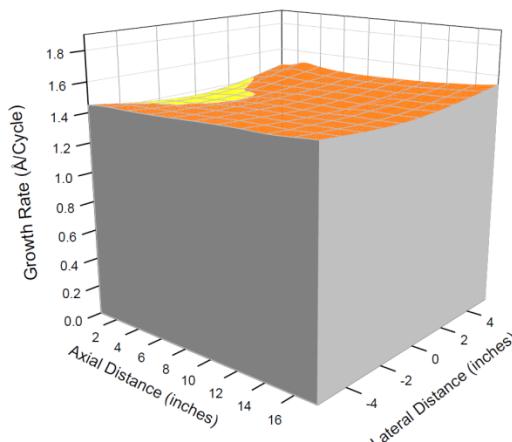
Conclusions- Why look beyond A/B/A/B... ?



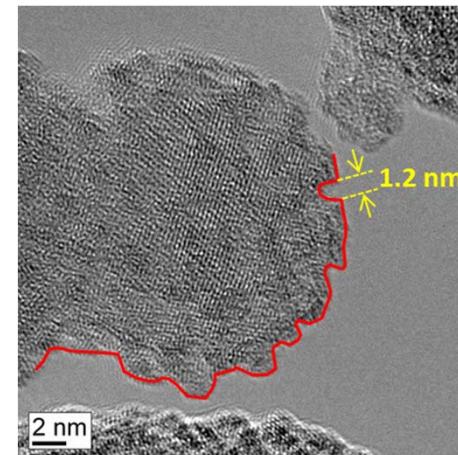
stripe coating



surface poisoning



precursor synergy



nanobowls



Acknowledgements

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A. Mane, H. Meng, Y. Lei, S. Jokela, S. Mohney,
A. Martinson, J. Hupp, M. Pellin, J. Hryn, A. Hryn, A. Xu, J.
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Questions?

